

Self-organization on surfaces: an overview

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<http://lab-neel.grenoble.cnrs.fr/themes/couches/ext/>



(1. Introduction)

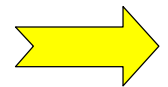
- **2. Self-assembled epitaxial growth**
- **3. Self-organized epitaxial growth**
- **4. 3D self-organization via multilayer stacking**
- **5. Perspectives of self-organization**
- **6. X-ray investigation of SO systems**

References





(1. Introduction)



2. Self-assembled epitaxial growth

3. Self-organized epitaxial growth

4. 3D self-organization via multilayer stacking

5. Perspectives of self-organization

6. X-ray investigation of SO systems

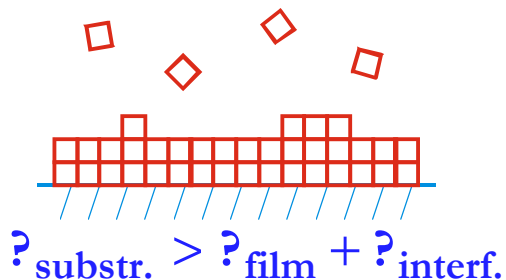
References



Macroscopic concept: surface energies

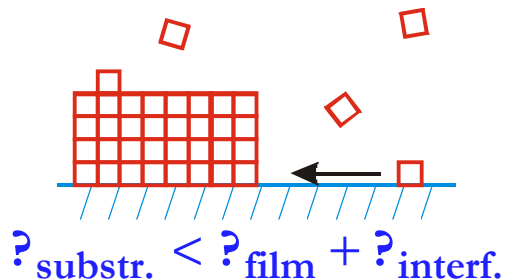
2D

Franck van der Merwe



3D

Volmer-Weber



E.Bauer, Z.Kristallogr.110, 372 (1958)

E.Bauer, Phys.Rev.B 33, 3657 (1986)

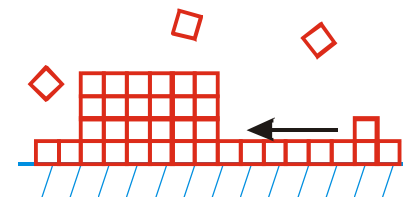
- Flat thin films: **high** substrate energy
- Islands (dots): **low** substrate energy



Another growth mode is frequently observed

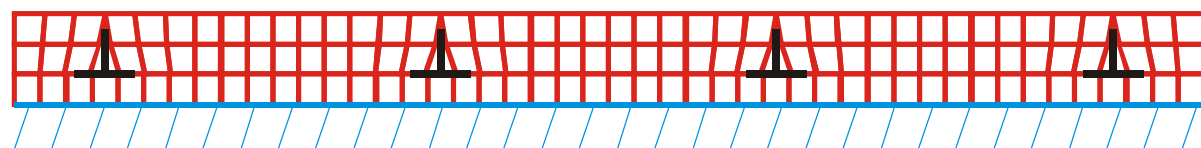
2D → 3D

Stranski-Krastanov

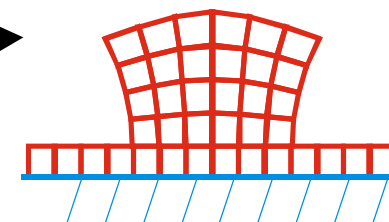


Microscopic concept: misfit accommodation

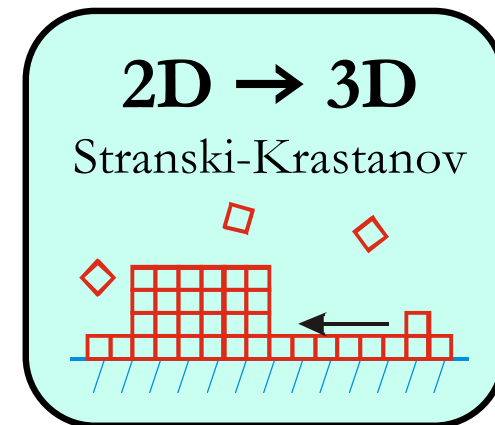
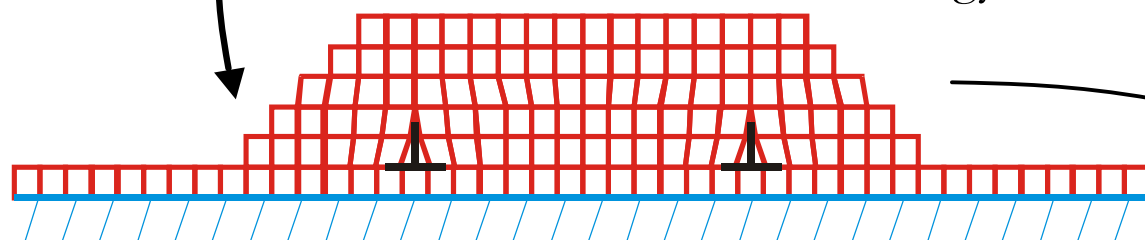
➤ High energy of dislocations



Misfit accommodation by elastic 3D relaxation



Additional effective interface energy



P.-O. Jubert *et al.*, *Phys. Rev. B* 64, 115419 (2001)

F. Tinjod *et al.*, submitted to *J. Alloy Comp.* (2002)

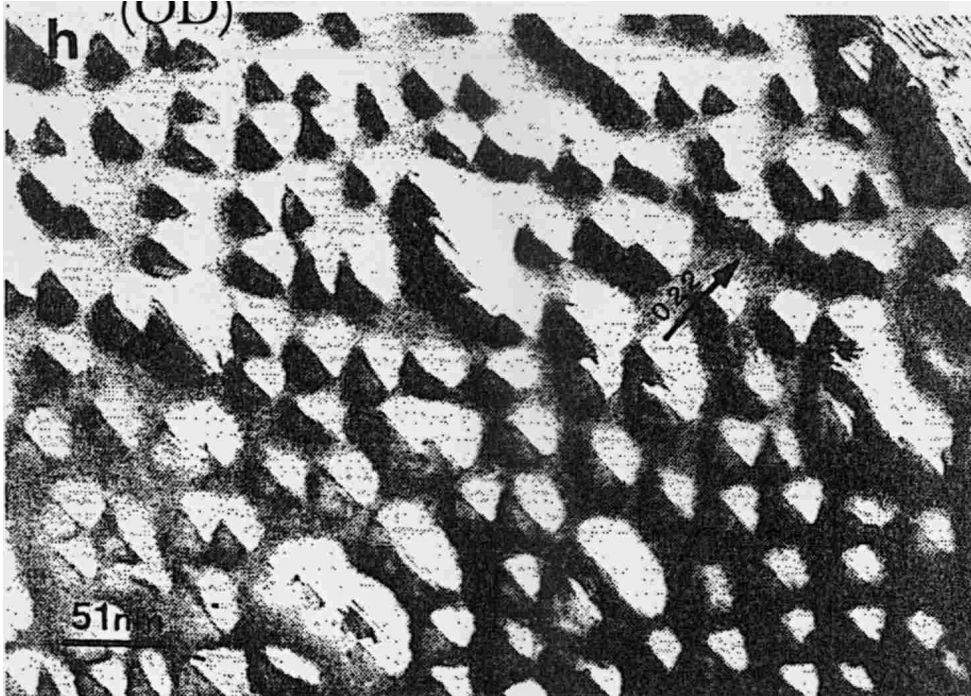
➤ Thickness-dependant surface stress

H.Ibach, *Surf.Sci.Rep.*29, 193 (1997)

➤ Many parameters for spontaneous island growth:
Self-assembly



➤ $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ quantum dots (OD)



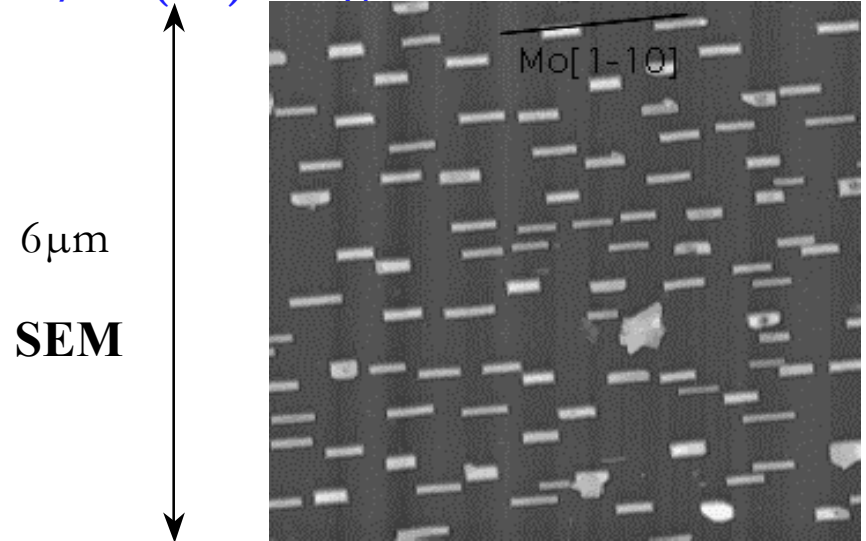
S.Z.Chang *et al.*, *J.Appl.Phys.*73,4916(1993)

➤ Laser diodes

Improvements : $\frac{?L}{L} \approx 4\%$

Nishi *et al.*, *Appl.Phys.Lett.*74, 1111(1999)

➤ Fe/Mo(110) elongated islands



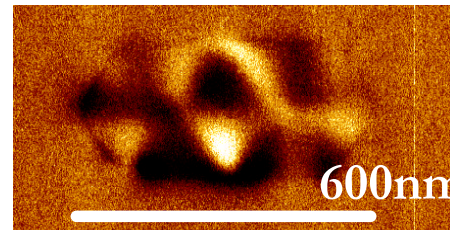
Target : SmFe_2

AFM

MFM.

Coll. Y. Samson

(CEA/France)



Target : Fe

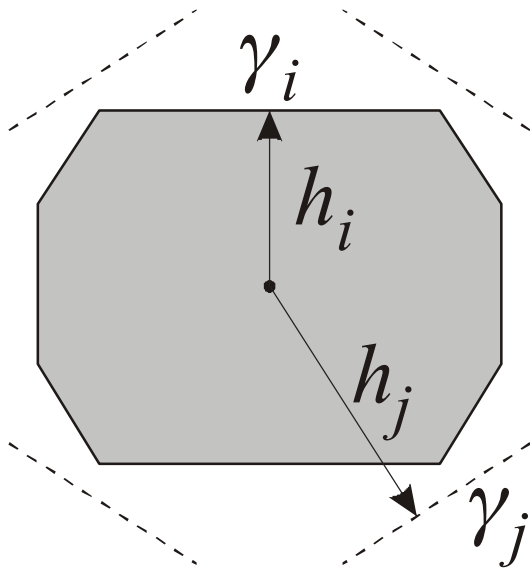
P.-O.Jubert *et al.*, LLN.



Wulff's theorem

Free crystal

$$\frac{\gamma_i}{h_i} = \text{Constant}$$

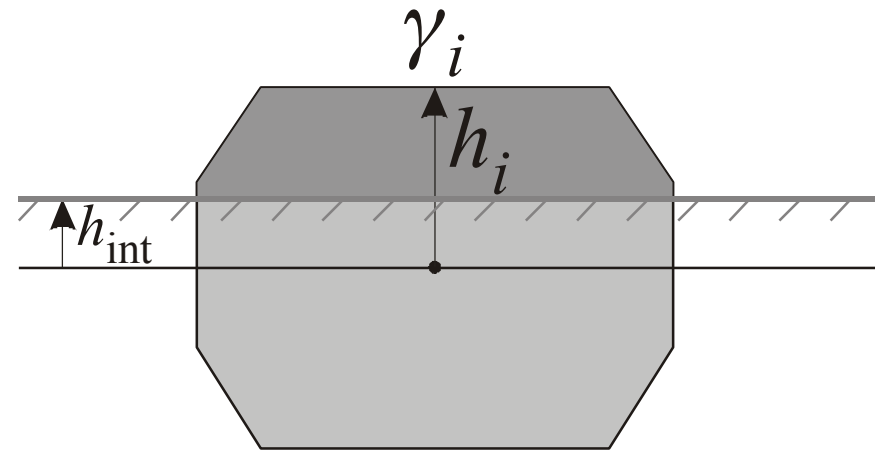


➔ No facets with high surface energy

Wulff Kaishev's theorem

Supported crystal (growth on surfaces)

$$\frac{\gamma_i}{h_i} = \frac{\gamma_S - \gamma_{\text{int}}}{h_{\text{int}}} = \text{Constant}$$

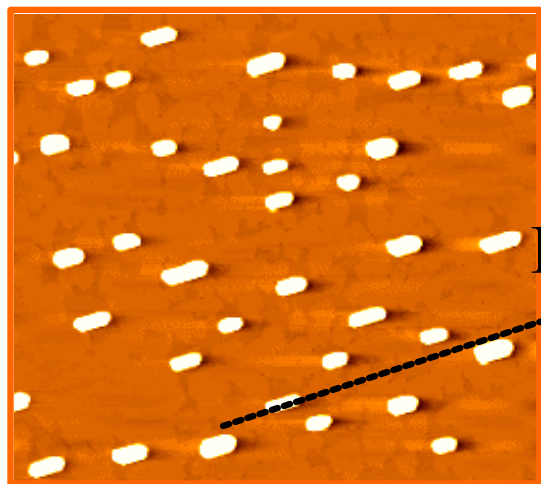


➔ Truncated crystal

With strain:

Simulations or more complex models (e.g. small dots)

P. Müller and R. Kern, Surf. Sci. 457, 229 (2000)

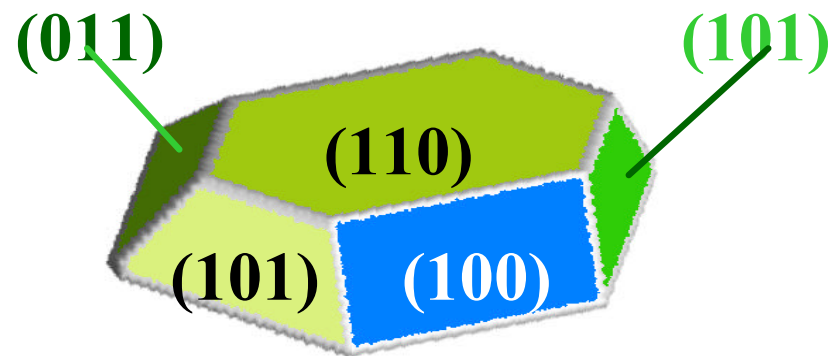
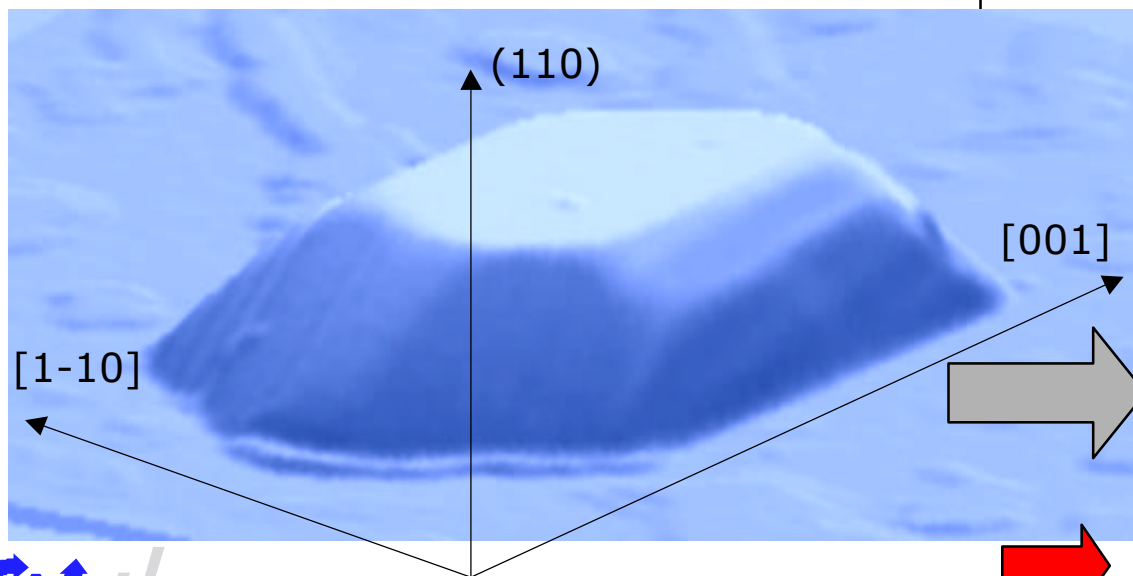
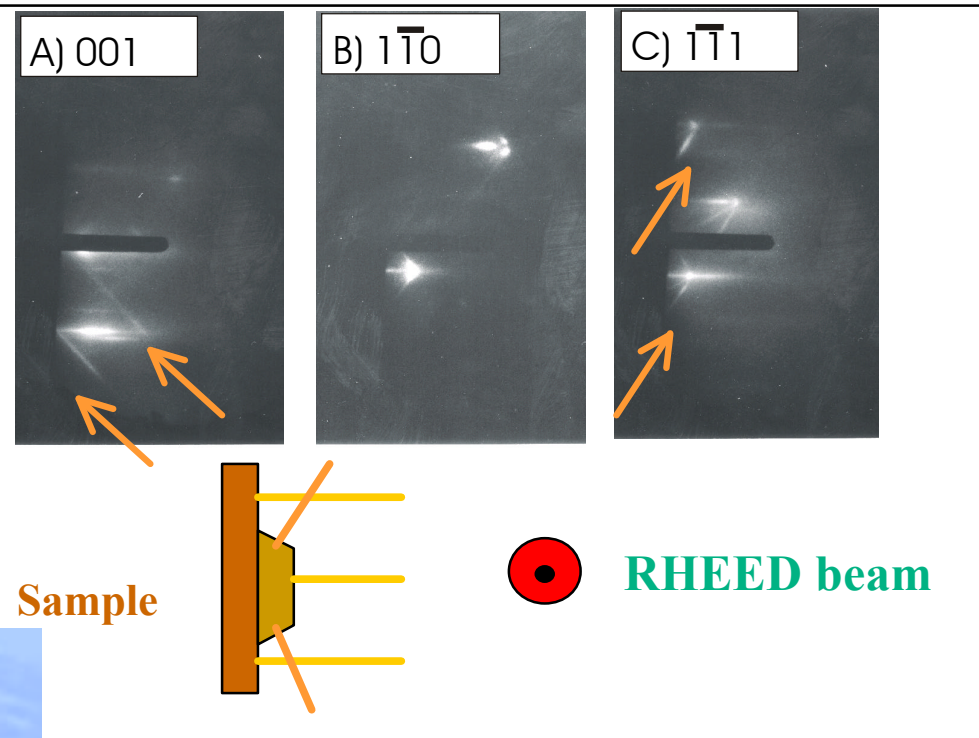


Fe/Mo(110)

Fe[001]

0 5 10 15 μm

AFM, 18mmx18mm



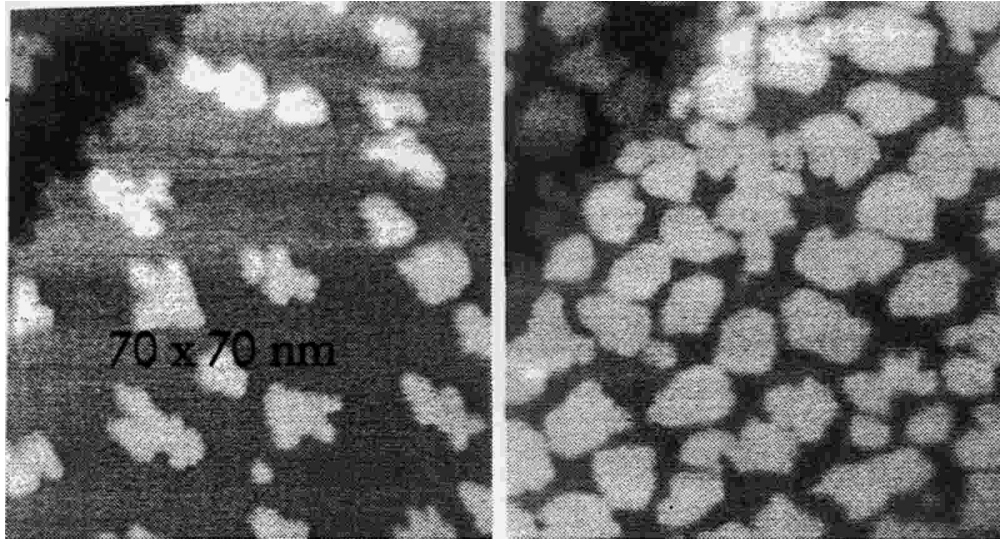
Model magnetic system



Very general phenomenon : many systems are suitable.

➤ Parameter : coverage $0 < x < 1$

Fe/W(110)



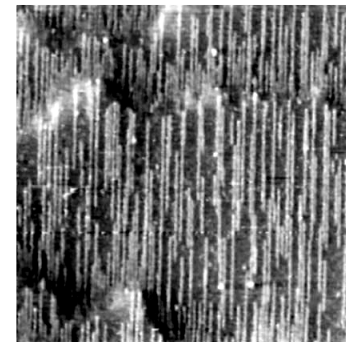
H.J.Elmers *et al.*, Phys.Rev.Lett.73, 898(94)

➤ « *Test of scaling theory at a two-dimensional Ising-like transition* »

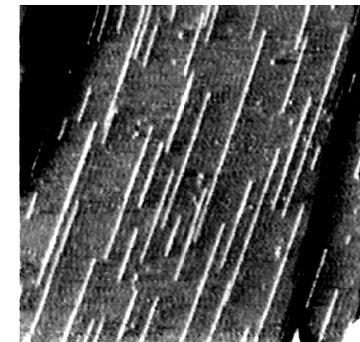
Ch. Würsch *et al.*, J. Magn. Magn. Mater 177-181, 617 (1998).

➤ Parameters: substrate symmetry and temperature

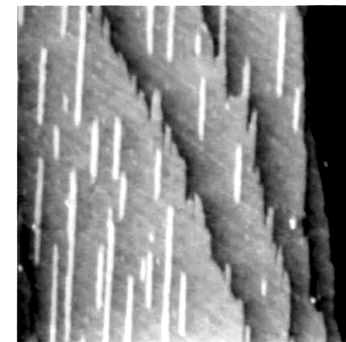
a) T = 265 K



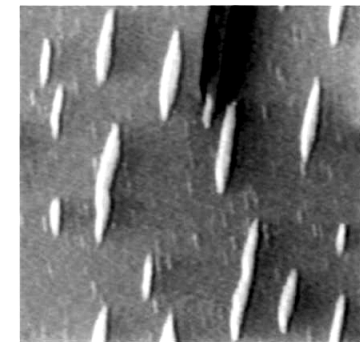
b) T = 300 K



c) T = 320 K



d) T = 350 K



Cu/Pd(110)

J.P.Bucher *et al.*, Europhys.Lett.27, 473(93)

➤ Size and density of the dots can be tuned nearly independently



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↪ Self-assembly + 'long-range' positional order between dots.

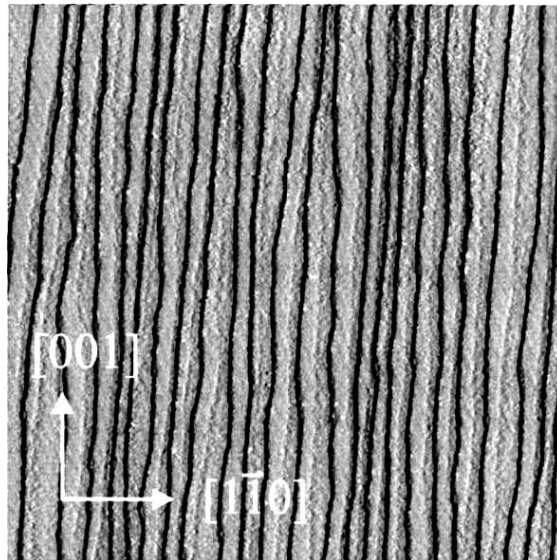
Dot-dot interactions \ll dot-substrate : the organization must be supplied by the substrate

STEP DECORATION

➤ Array of atomic steps. Ex: stripes (1D)

Vicinal
Fe(110)/W(110)

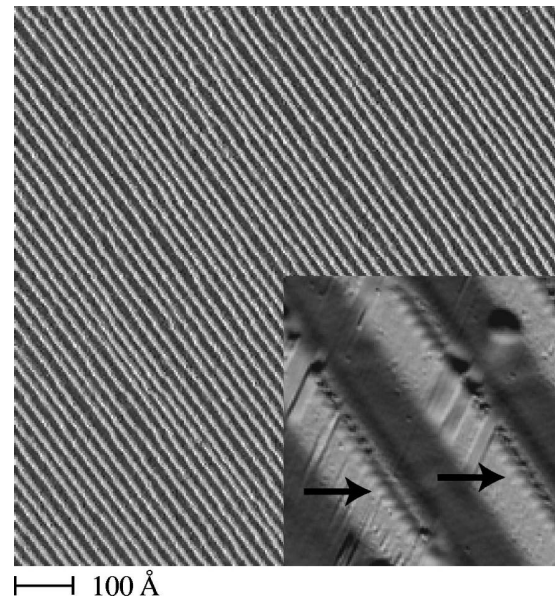
250 x 250 nm



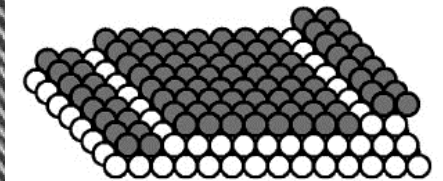
J.Hauschild *et al.*, *Phys.Rev.B*57, R677(1998)

↪ Magnetic order in 1D
(stabilized by dipolar interactions)

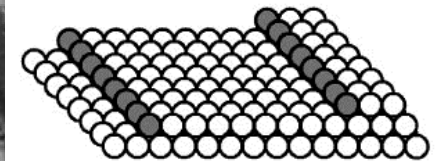
➤ Ex: Stripes and wires (1D)



Terraces \sim 1 ML



Chains \sim 0.12 ML



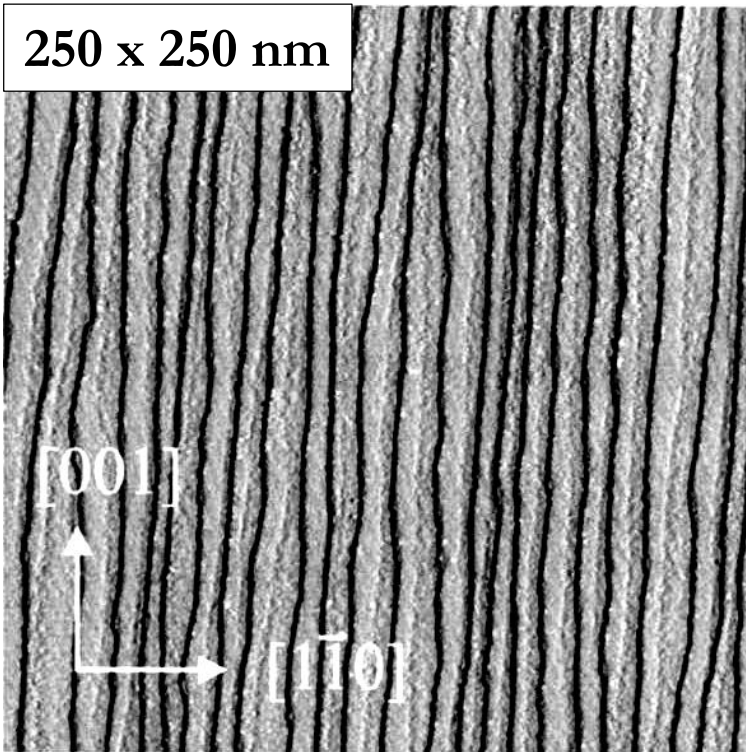
A. Dallmeyer *et al.*, *Phys.Rev.B* 61(8), R5153 (2000).
Co(250K - 0.12ML)/Pt(997)

↪ Magnetic order and anisotropy in 1D



Example: Vicinal
Fe(110)/W(110)

Thickness = $0.5AL$

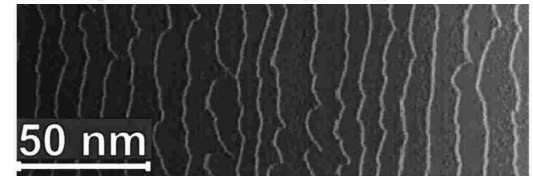
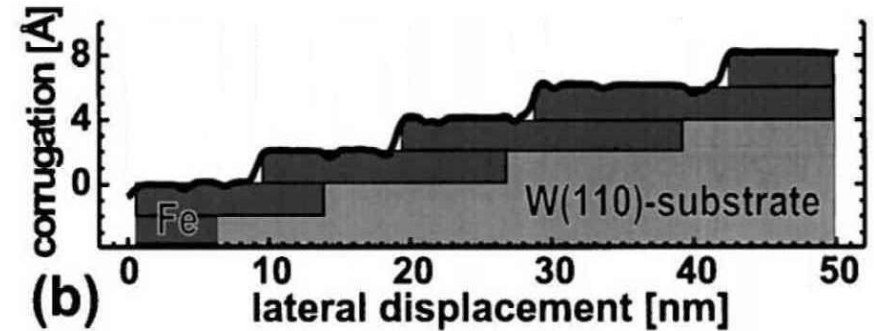


Magnetic ordering
in 1D
(stabilized by
dipolar interactions)

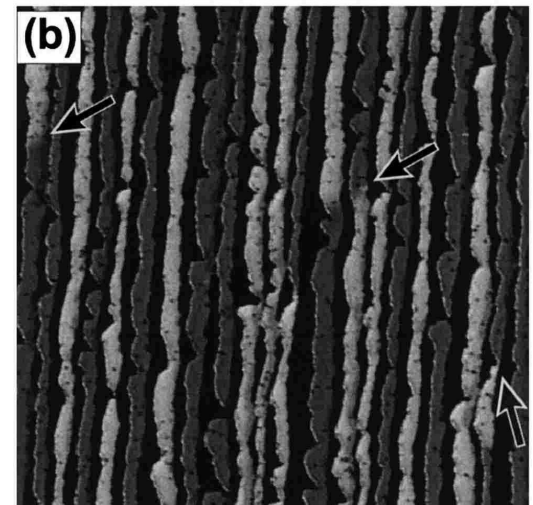
$T_c = 179K$

J.Hauschild *et al.*, Phys.Rev.B57, R677(1998)

Thickness = $1.5AL$



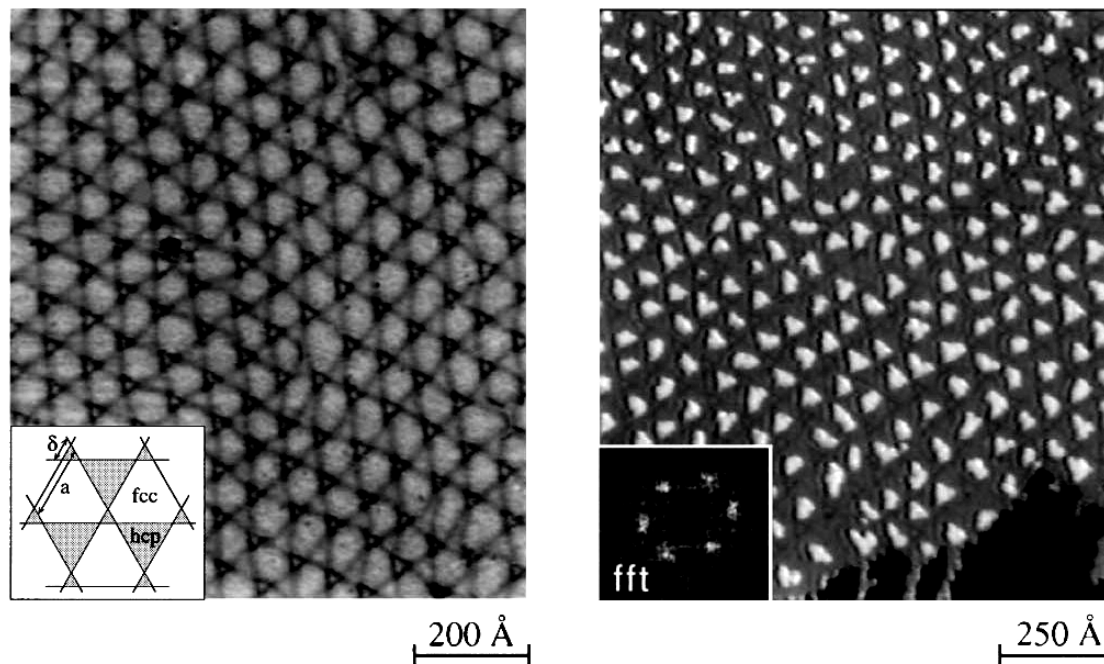
Spin-Polarized
Scanning
Tunneling
Spectroscopy
(low temp.)



M. Bode *et al.*, J. Electr. Spectr. Rel. Phenom. 114– 116, 1055 (2001)



➤ a) **Overlayer dislocations array**, Ex: dots (OD)



H.Brune *et al.*, Nature **394**, 451 (1998)

Ag(110K)/Ag(2ML, 400K annealed at 800K)/Pt(111)

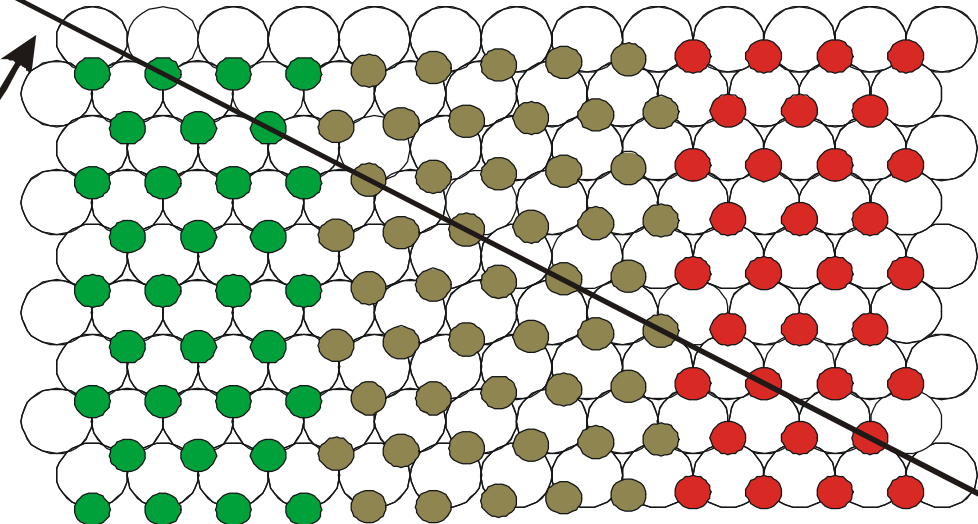
➤ Also : **improvement of size uniformity of the dots**

D.Y.Petrovykh, Surf.Sci. 407, 189 (1998)



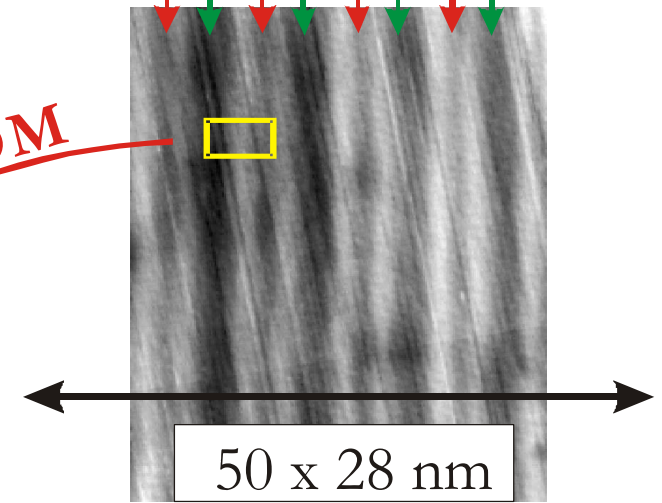
Planar view of Au(111)

FCC HCP



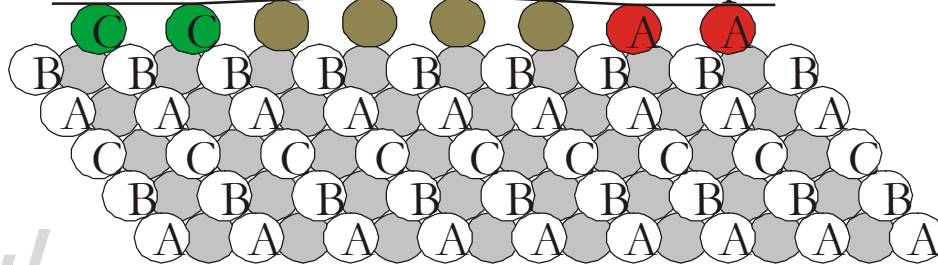
FCC HCP

ZOOM

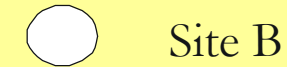


Cross-sectional view

fcc : ABC Corrugation hcp : ABA



Second layer atoms

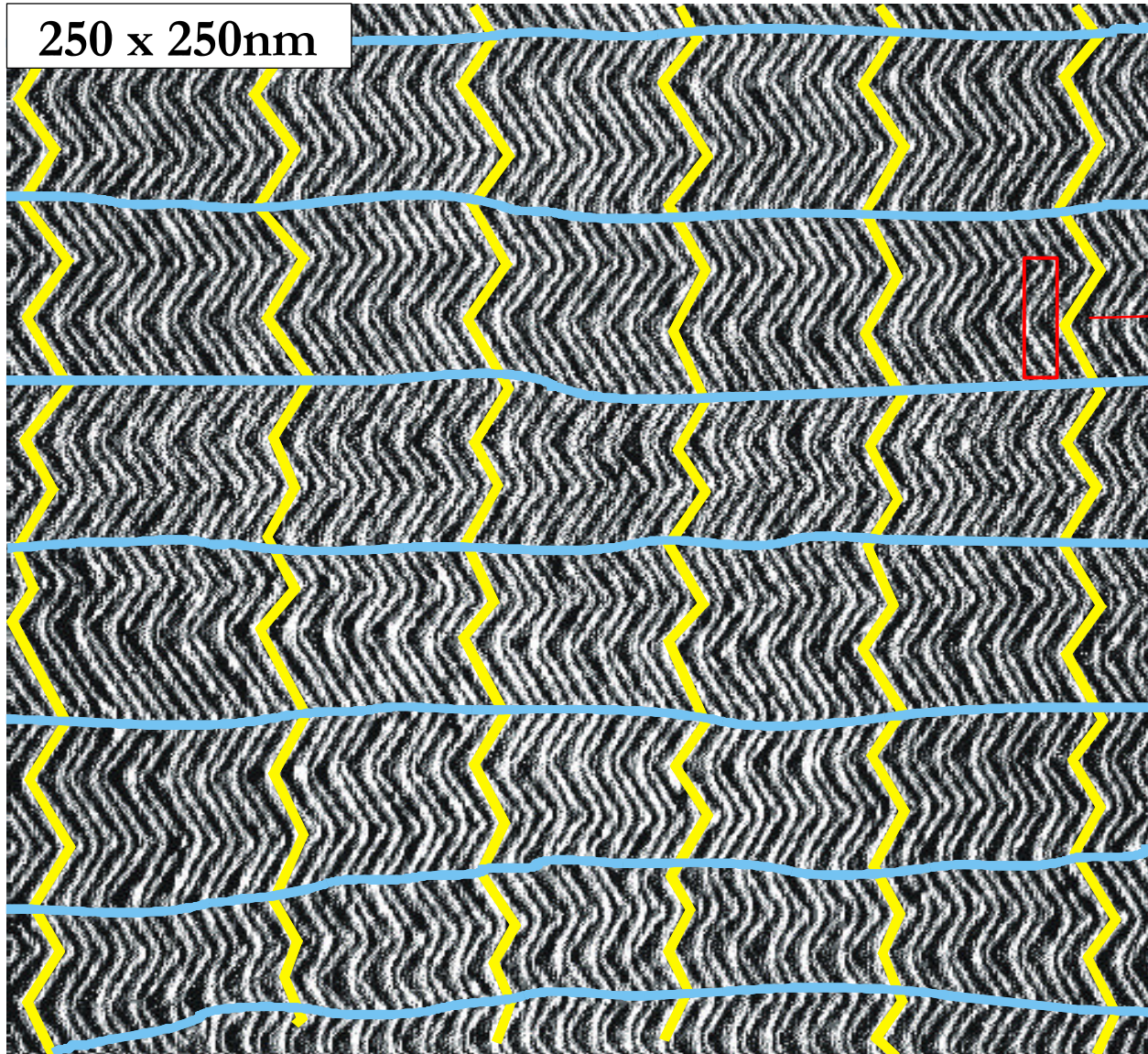


Atoms of the topmost layer

- Site A
- Site C
- Saddle position

(smaller diameter for clarity only)





Corrugation $\sim 0.2 \text{ \AA}$

Unit cell size :

$\sim 7.5 \times 25 \text{ nm}$

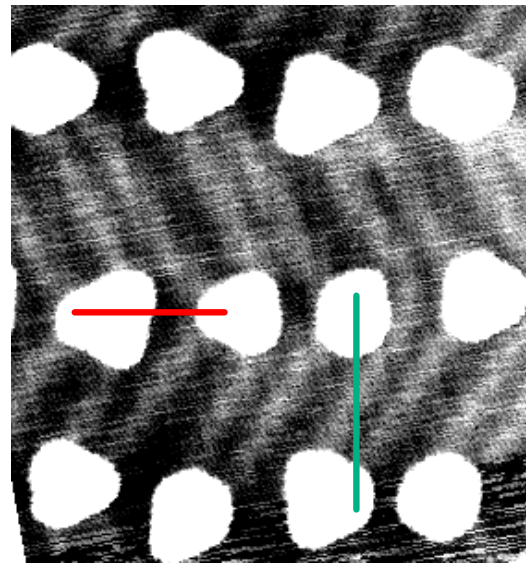
 Isotropic surface relaxation

J. V. Barth et al., Phys. Rev. B 42 (15), 9307 (1990)

A.R. Sandy et al., Phys. Rev. B 43 (6), 4667 (1991)



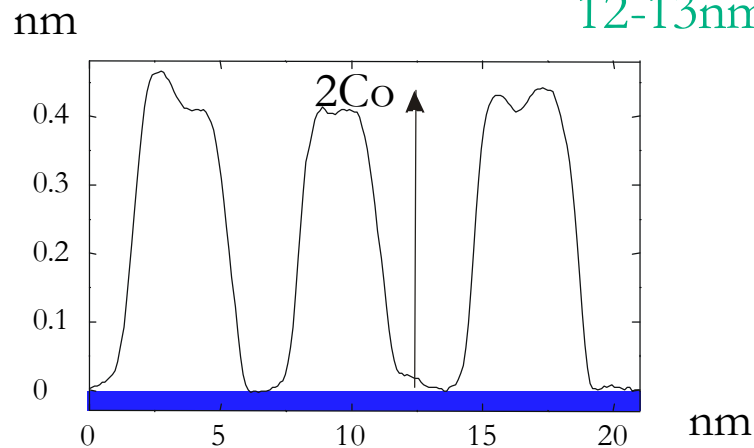
- Co, Ni, Fe :
Nucleation at the
elbows of the chevrons



7.5nm

(0.20AL Co@300K)

12-13nm

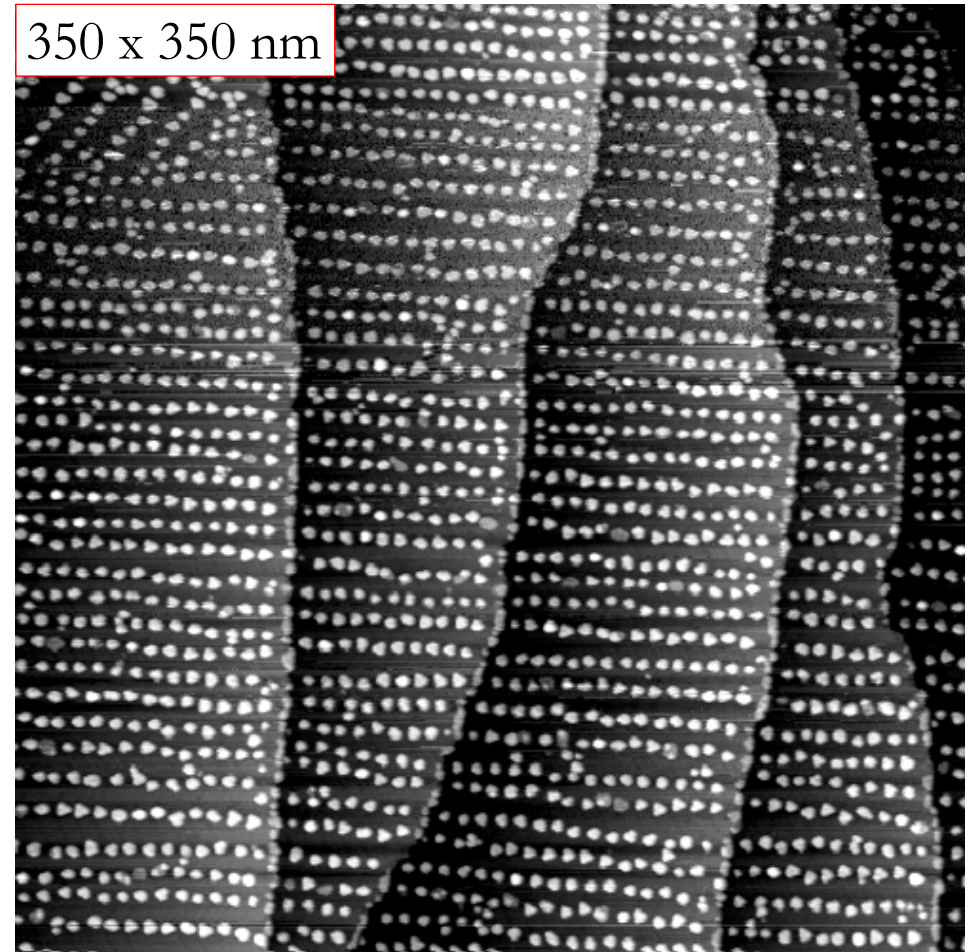


Fe, Ni : 1 AL-high dots

D.D. Chambliss et al., PRL **66**, 1721 (1991)

B.Voigtlander et al., PRB **44**, 10354 (1991)

350 x 350 nm

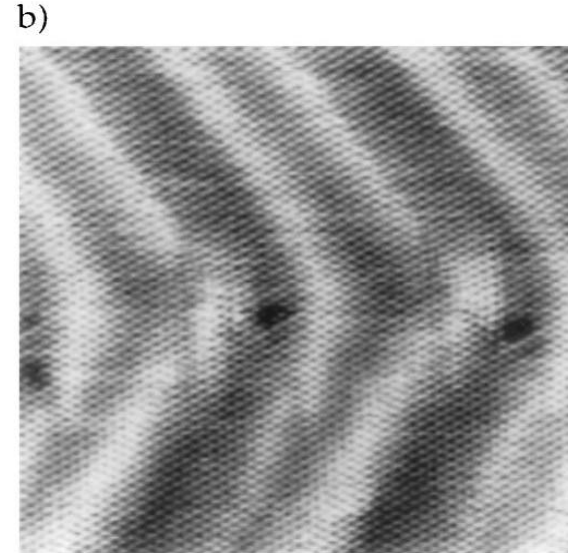
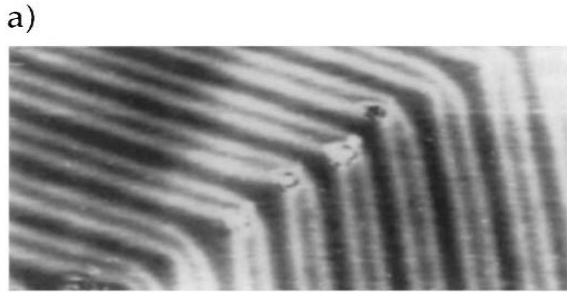


- Medium-ranged organization
- Steps do not necessarily disturb the order
[see also:
V.Repain, Europhys. Lett., **47** (4), 435 (1999)]



Fe, Co, Ni (etc.) nucleation: atomic place exchange mechanism with Au atoms

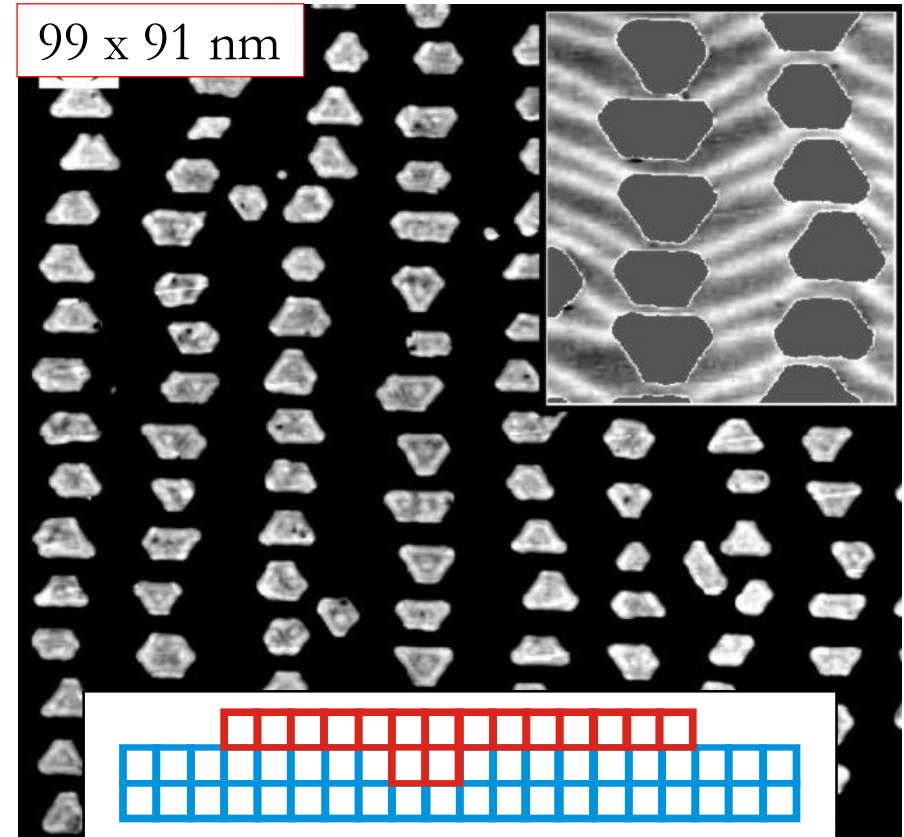
Example: 0.002ML Ni@300K



Element	Surface free energy (eV)	Heat of sublimation (eV)
Ag	0.50	2.95
Al	0.56	3.39
Cu	0.69	3.51
Au	0.72	3.79
Ni	0.90	4.45
Co	0.94	4.40
Fe	0.96	4.32

J.A.Meyer et al., Surf.Sci. **365**, L647 (1996)

0.25ML Ni@300K : 1ML-high dots

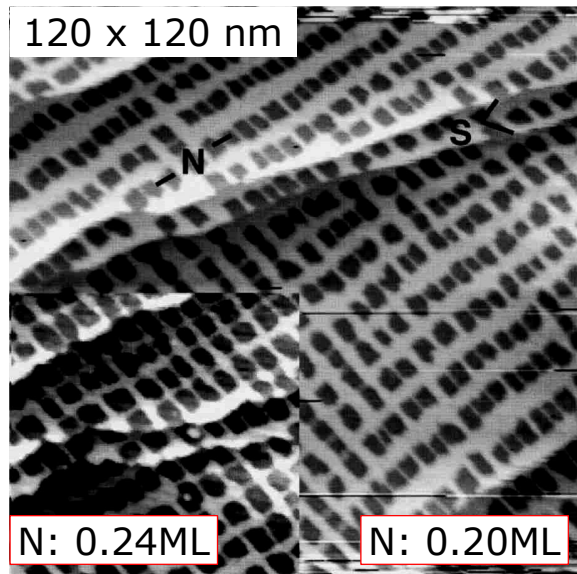


W.G.Cullen et al., Surf.Sci. **420**, 53 (1999)

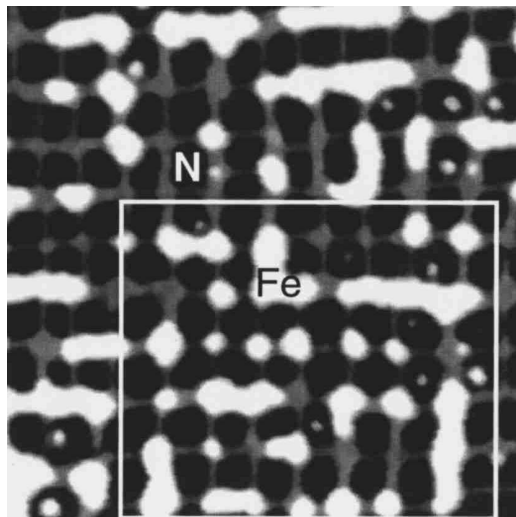
Leading parameter : deposit has a higher surface energy.
(and Au atoms stress near chevrons)



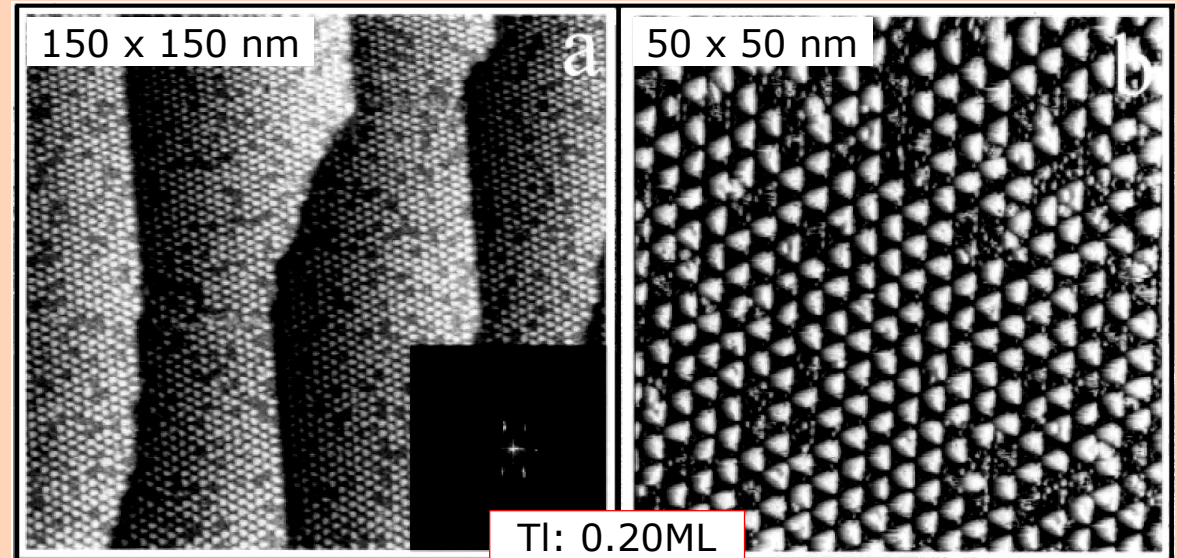
➤ Self-organized adsorption: N on Cu(100)



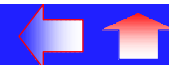
T.M.Parker, Phys.Rev.**B56**, 6458(1997)



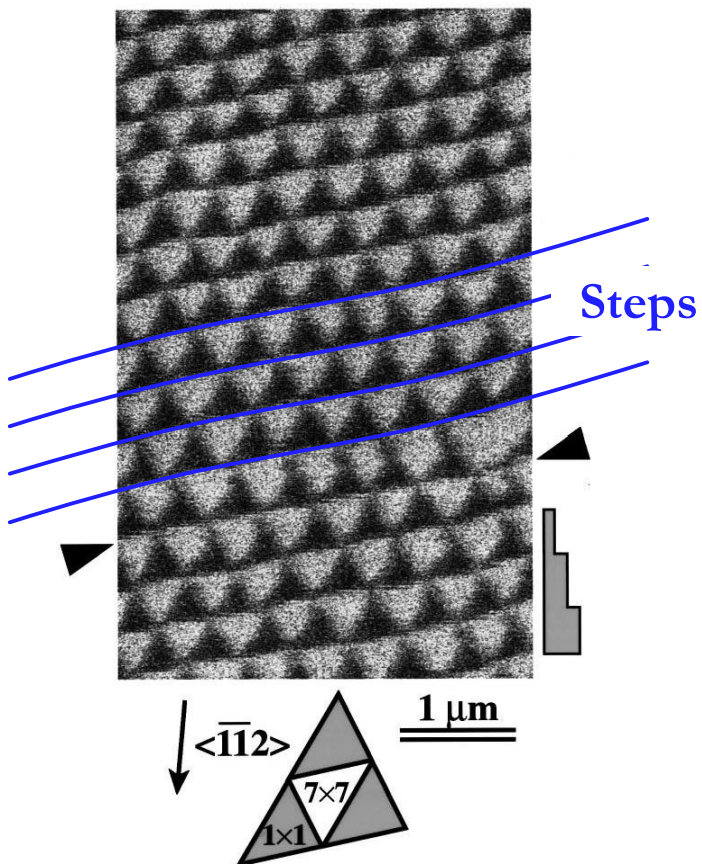
➤ Self-organized growth on reconstructions
Tl on Si(111) 7x7



L.Vitali, Phys.Rev.Lett.**83**(2), 316 (1999)



- Superstructure of reconstructions: **7x7 and 1x1 triangles** on Si(111), misoriented along $\langle 11-2 \rangle$



H.Hibino, Phys.Rev. **B58**(12), R7500 (1998)

- **Co on vicinal Au(111)**

Steps and reconstructions

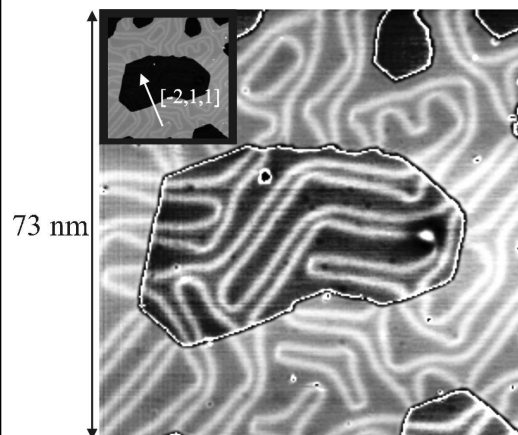


FIG. 4. STM image of a few vacancies islands. $T=300$ K. In inset, the raw STM image. The same image is shown where the corrugation due to the terrace levels has been subtracted in order to enhanced the reconstruction lines.

Reconstructions lie perpendicular to steps

V.Repain, Europhys. Lett., **47** (4), 435 (1999)
V.Repain, ACSIN5 proceedings

1ML Co

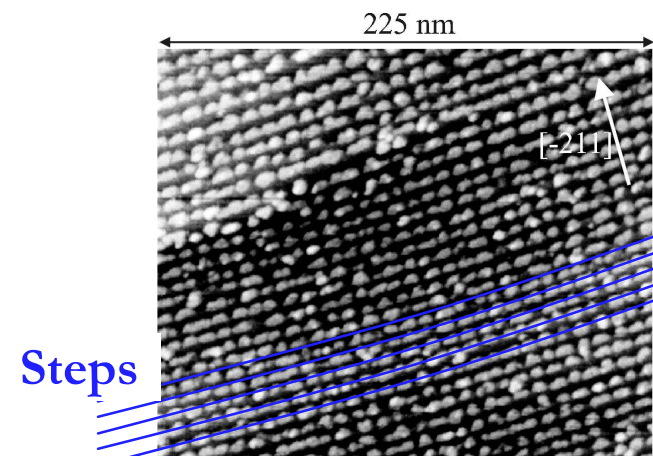
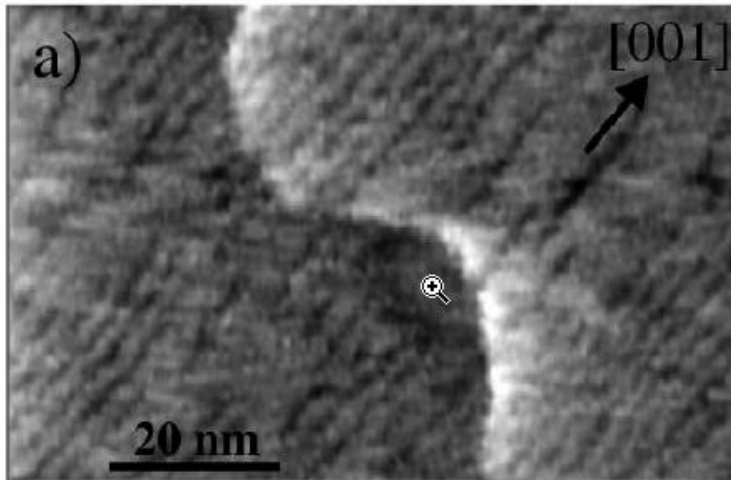


FIG. 6. Rectangular lattice (7 nm x 8 nm) of cobalt clusters on a vicinal surface misoriented from 1.7° with respect to Au(111) towards the $[-211]$ azimuth. Cobalt coverage is 1 ML. Arrow indicates the descending steps direction.

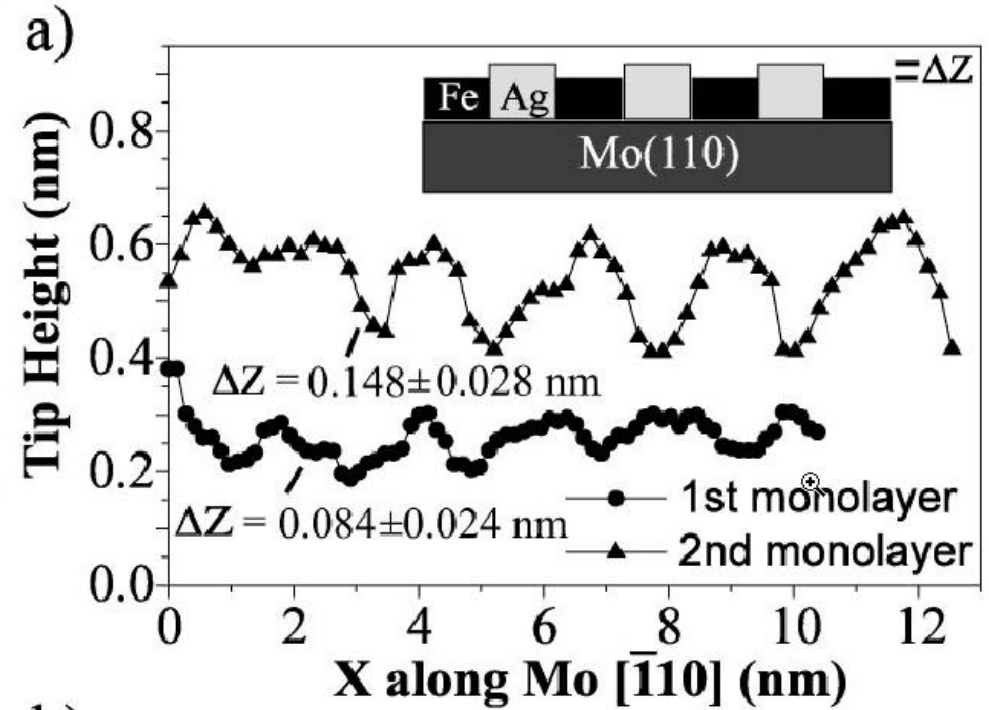
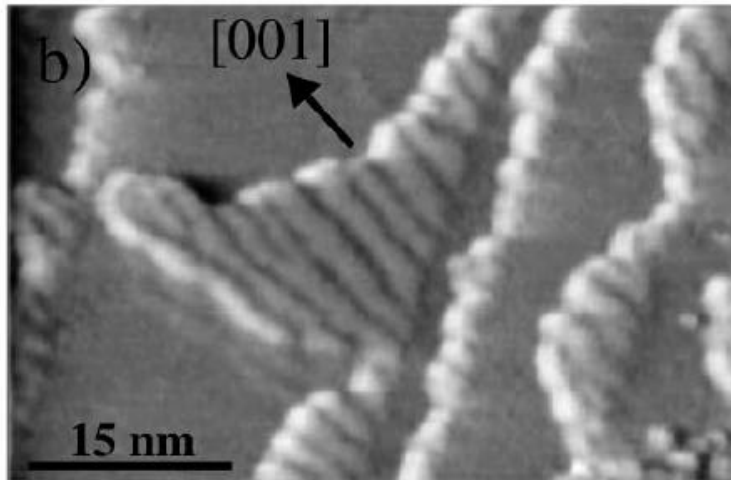
Nucleation both at steps and at reconstructions

Lateral modulation in ultrathin films

FeAg/Mo(110)
1AL



CoAg/Mo(110)
0.3AL



E. D. Tober et al., PRL81, 1897 (1998)



Stéphane ANDRIEU: possible link with Fe/V(110) ?



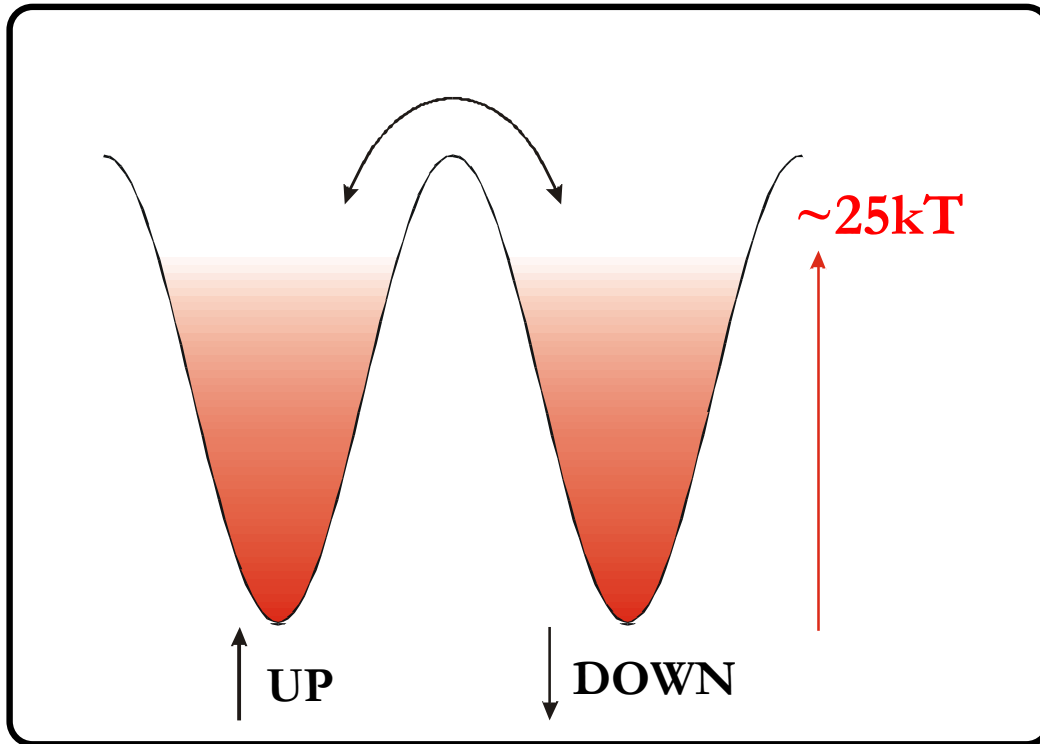
- Self-organization generally from substrate, not from deposit !
- Relies on surface science fundamental investigations

- combine
- Surface reconstructions
 - Overlayer array of dislocations
 - Adsorbates patterns
 - 1D or 2D array of steps
 - Steps (or bonding ?) and reconstructions
- Better size control
-

- Good pattern does not necessarily imply good overgrowth

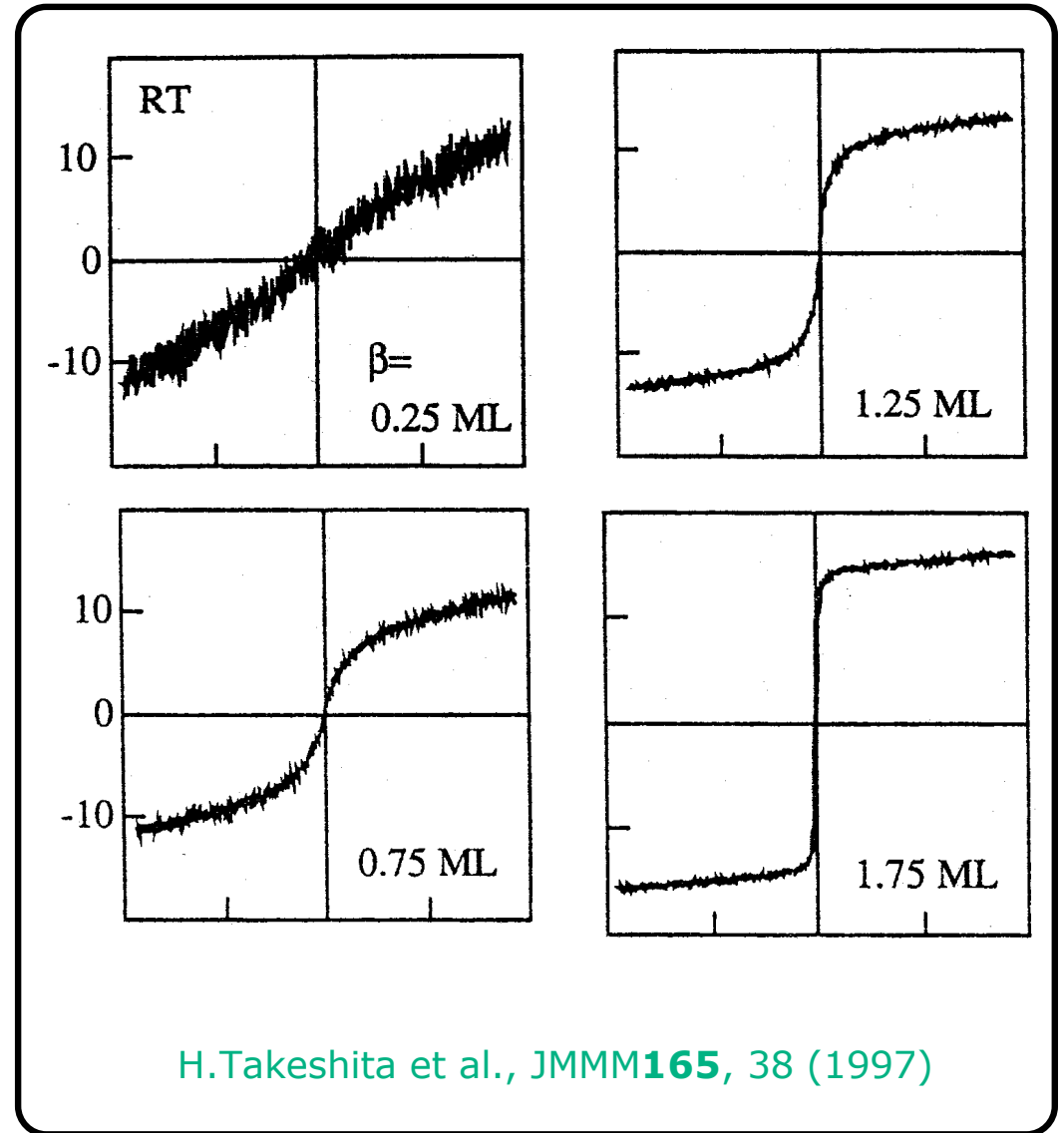


Anisotropy barrier \sim KV



Blocking temperature $T_b \sim 20K$
 H.Dürr et al., PRB59, R701 (1999)

Example: Co/Au



H.Takeshita et al., JMMM165, 38 (1997)





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3. Self-organized epitaxial growth

 **4. 3D self-organization via multilayer stacking**

5. Perspectives of self-organization

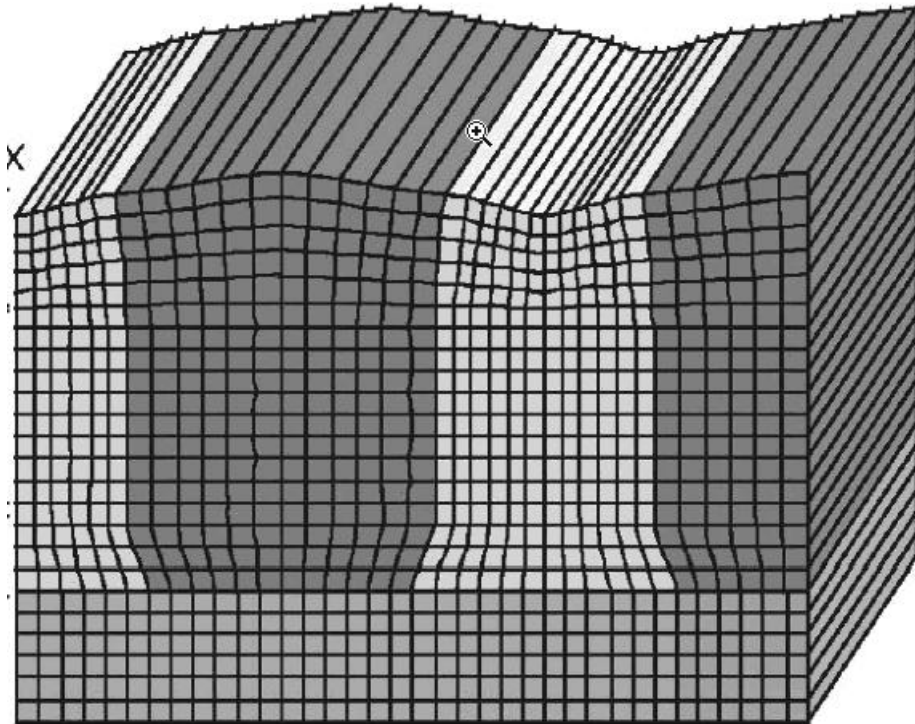
6. X-ray investigation of SO systems

References



Principle

Strain release
Here: accumulation during growth

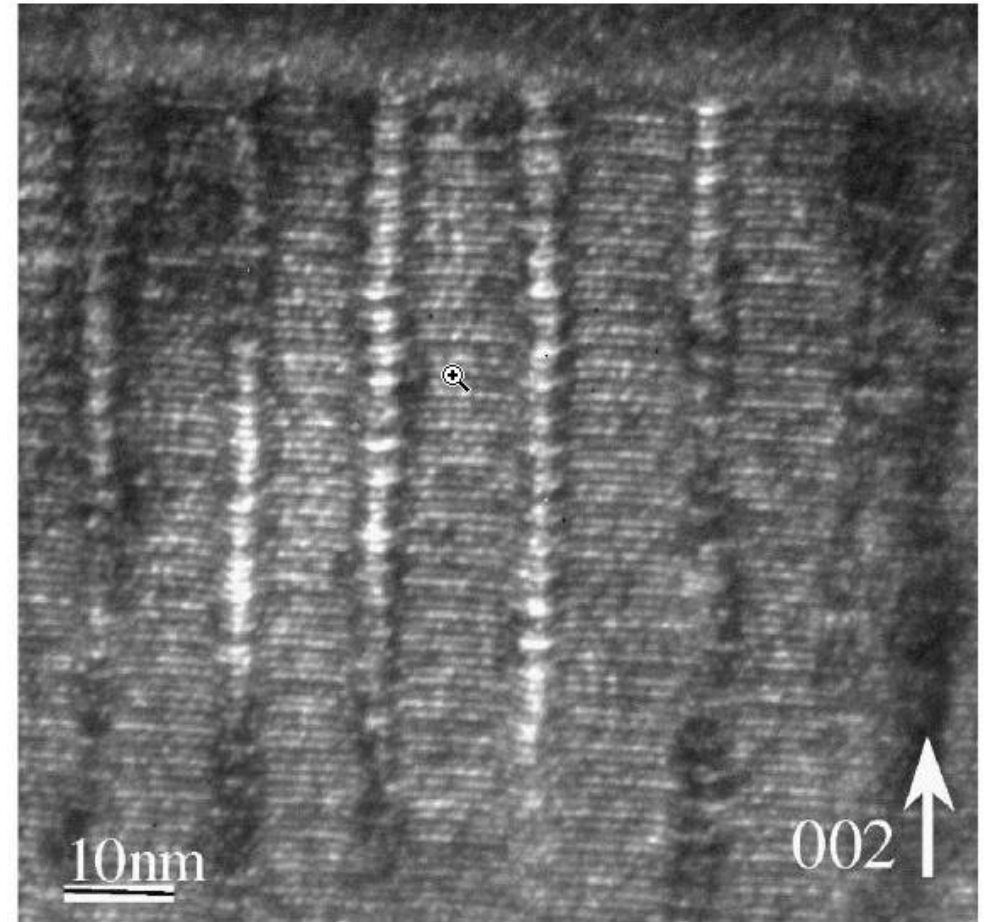


R. D. Twisten et al, PRB60, 13619 (1999)

[Cf Grinfeld instability: M. A. Grinfeld, Dok. Akad. Nauk SSSR 290, 1358 (1986)]

Experiments

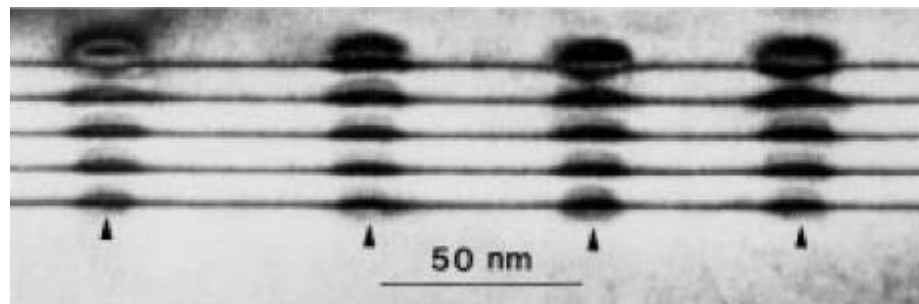
InAs/AlAs short-period multilayers



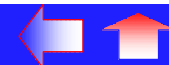
R. D. Twisten et al, PRB60, 13619 (1999)

InAs / GaAs(100)

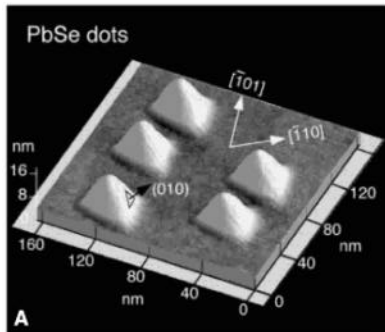
- Strain field in spacer layer :
 - ↻ vertical stacking of dots



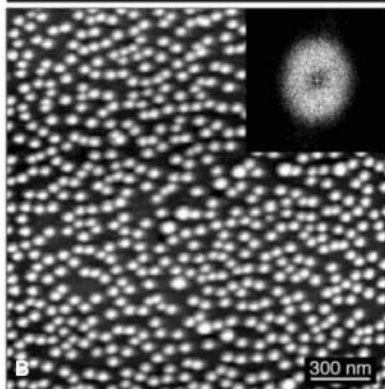
Q.Xie, Phys.Rev.Lett.75(13), 2542 (1995)



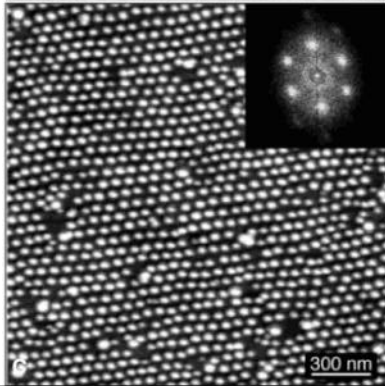
➤ From 2D assembly to 3D- organization



Zoom :
faceted dots



Single layer :
Self-assembly,
no organization.



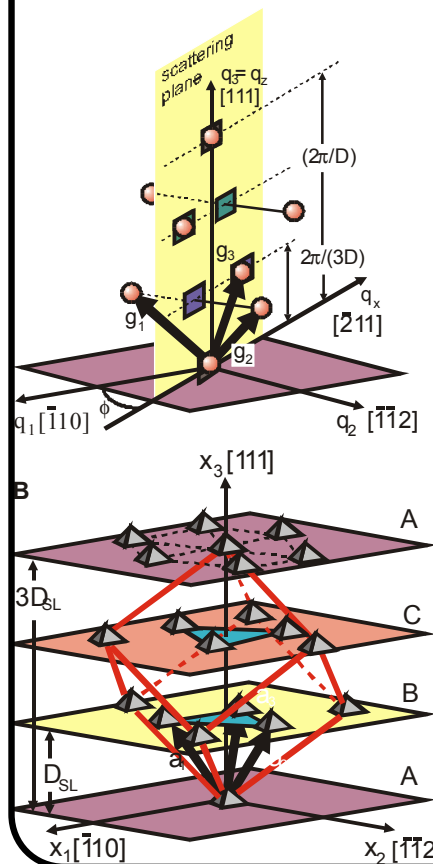
Multilayers :
improvement of
the organization.

(After 60 layers)

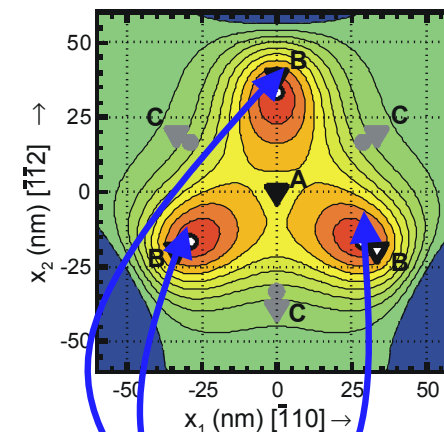
PbSe / PbTe(111)

➤ Anisotropic elastic media
↳ f.c.c. superstacking, not vertical.

X-Ray diffraction



Anisotropic in-plane
distribution of
elastic energy density



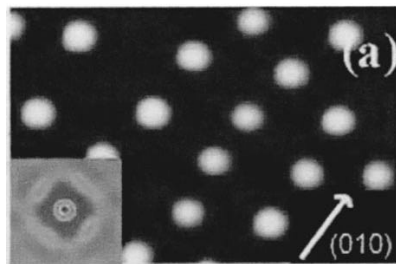
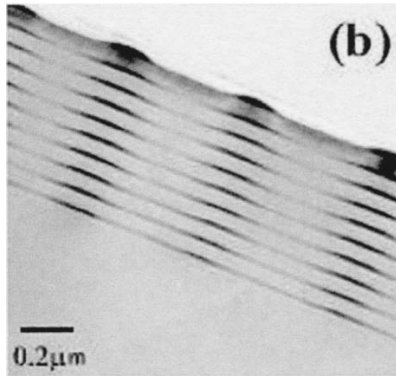
Misfit reduced by 2%
↳ preferential nucleation



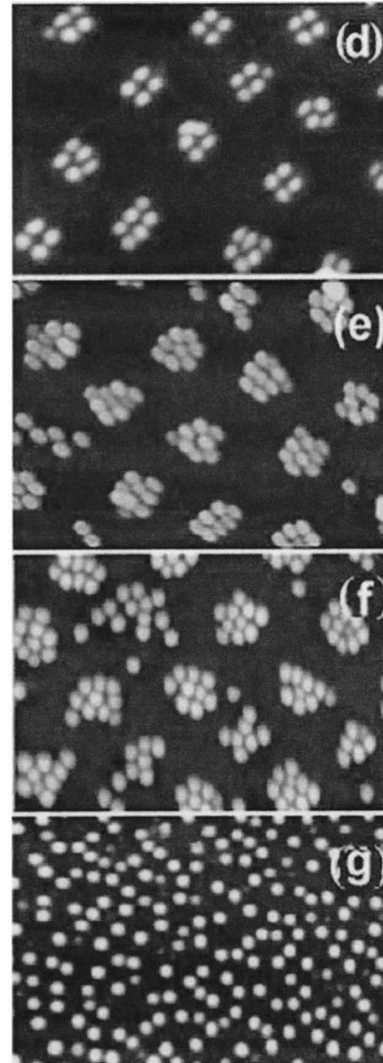


Step 1 multilayers for organization

Ge islands/Si(001)



Step 2 use as a template



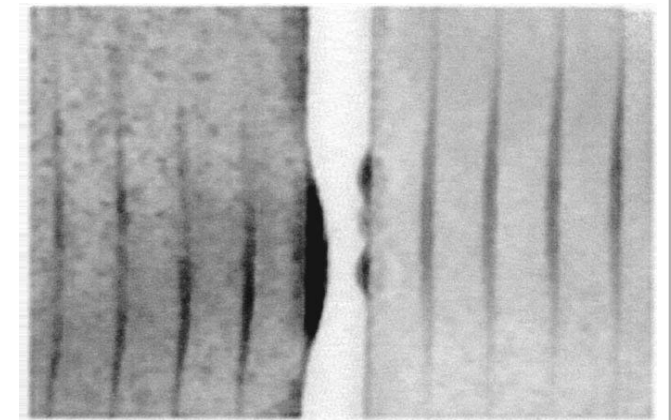
35nm

45nm

65nm

200nm

HREM view



Template

Overgrowth

G. Capellini *et al.*, APL82, 1772 (2001)

Laboratoire Louis Néel, Grenoble, France.

Olivier Fruchart - 2/09/2003 - p.28

<http://lab-neel.grenoble.cnrs.fr/themes/couches/ext/>

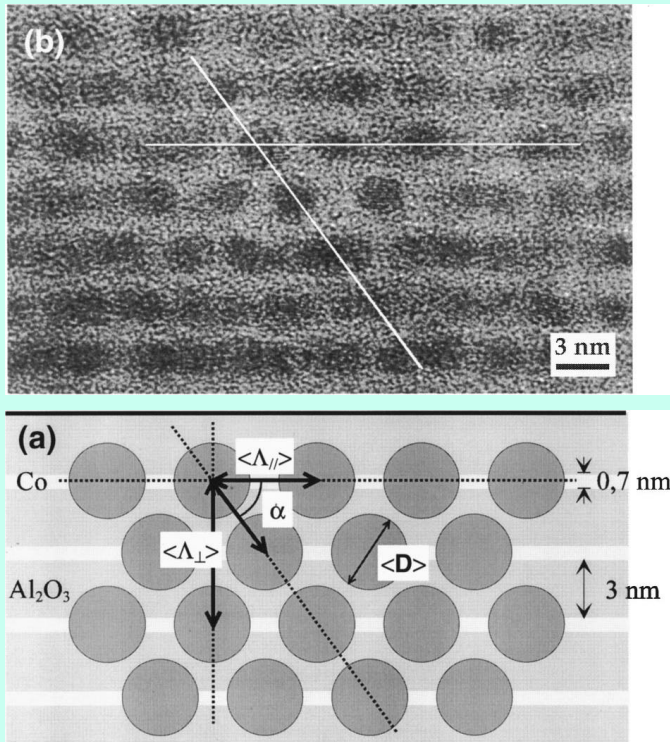


Co/Al₂O₃ granular system (sputtering)

(Co: 0.7 nm/Al₂O₃: 3 nm)₁₄

REAL SPACE

TEM cross-section (Sequential sputtering)



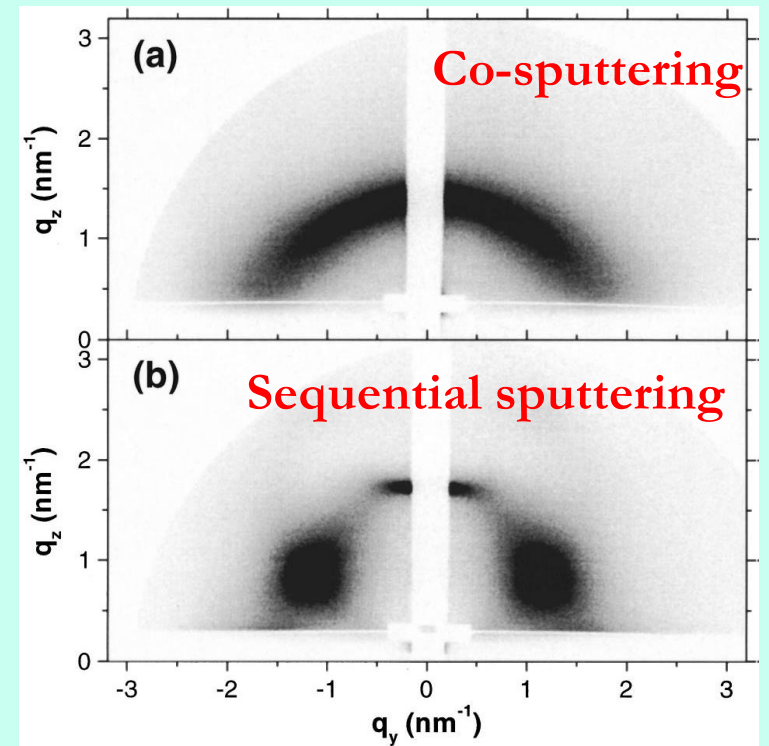
➤ FCC vertical stacking (not epitaxial !)

D. Babonneau, Appl. Phys. Lett. 76, 2892 (2000)

Laboratoire Louis Néel, Grenoble, France.

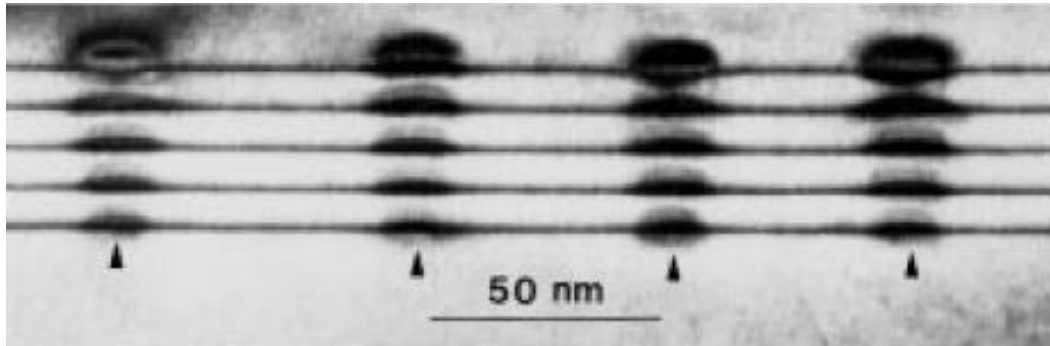
RECIPROCAL SPACE

GISAXS:
Grazing Incidence Small Angle
X-Ray Scattering

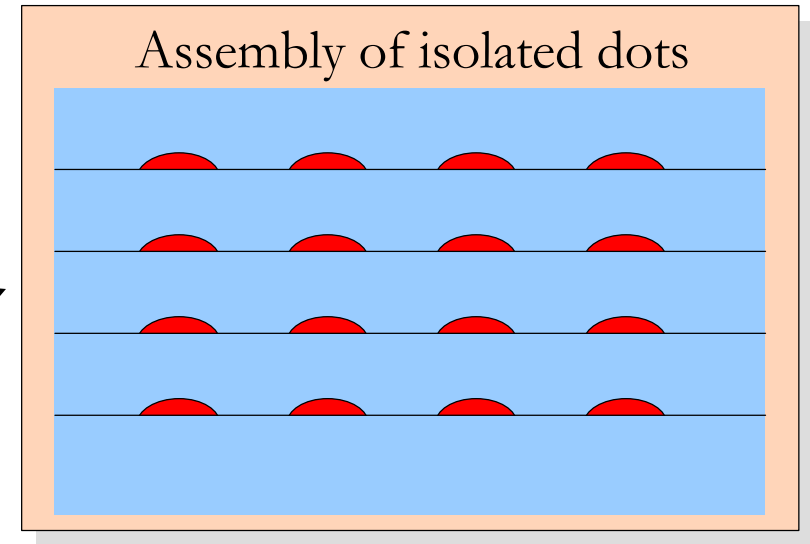




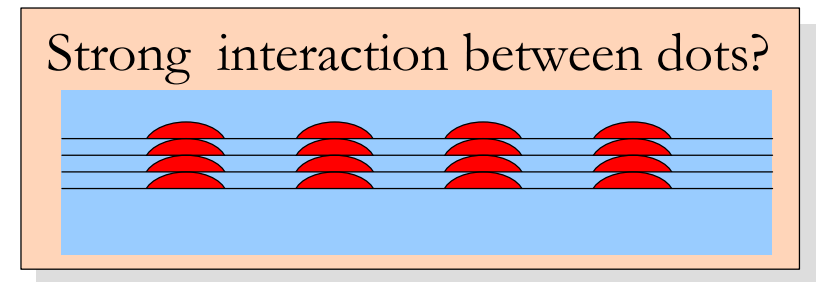
➤ Vertical 3D self-organization of $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$:



Q.Xie et al., Phys.Rev.Lett.75(13), 2542 (1995)

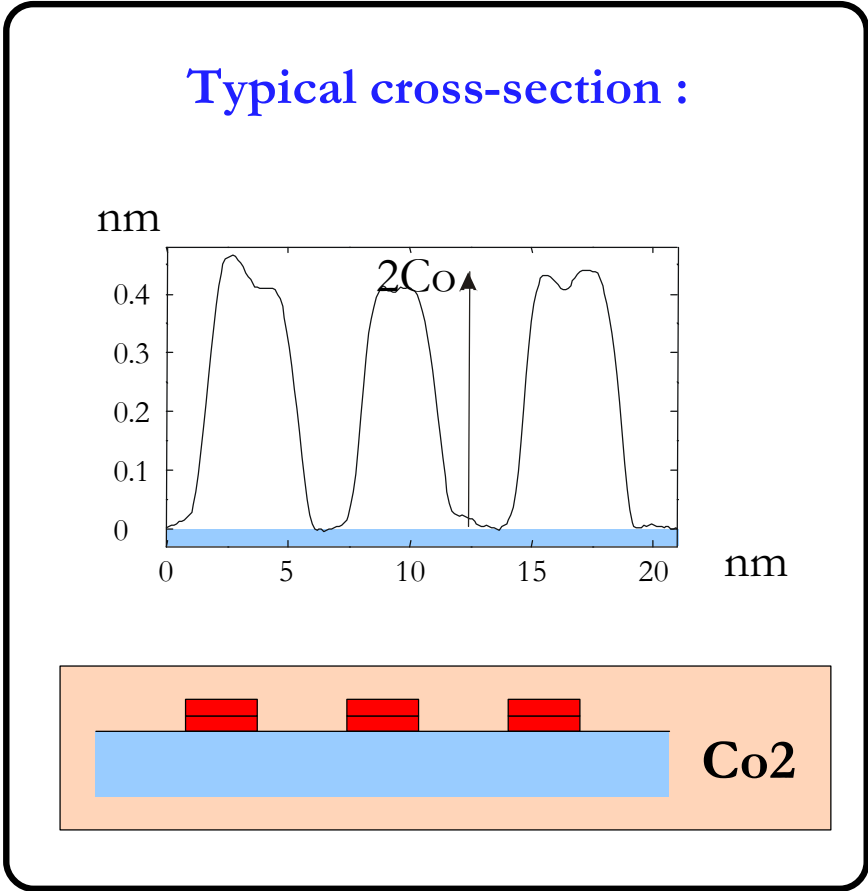
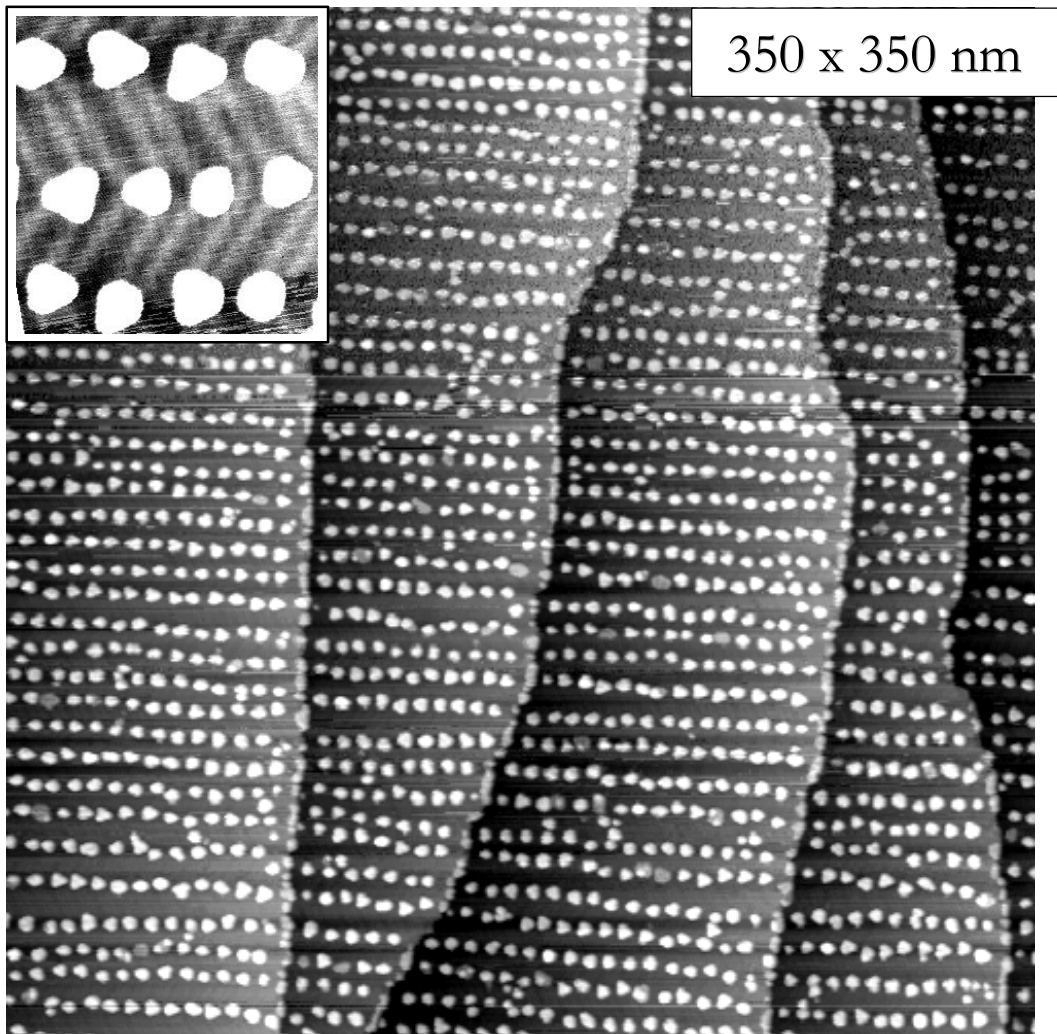


Thining the spacer layer



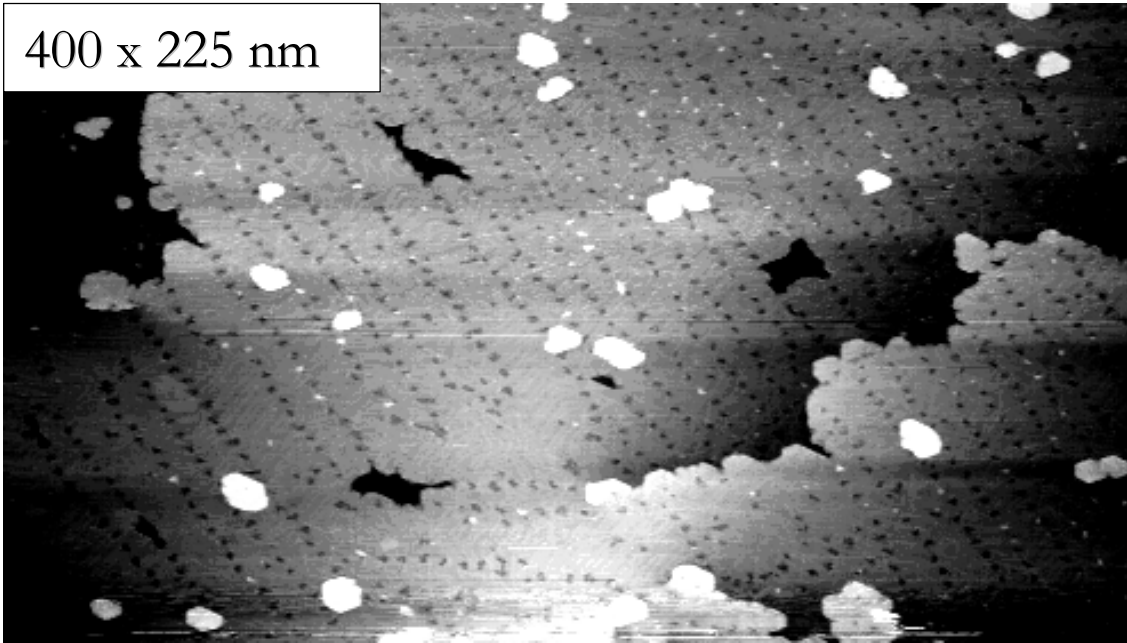
- superparamagnetism overcome ?
- Enhanced magnetic signal

➤ Step 1 : 0.2ML Co @300K



➤ Step 2 : 3.8ML Au @375 \nearrow 410K

400 x 225 nm



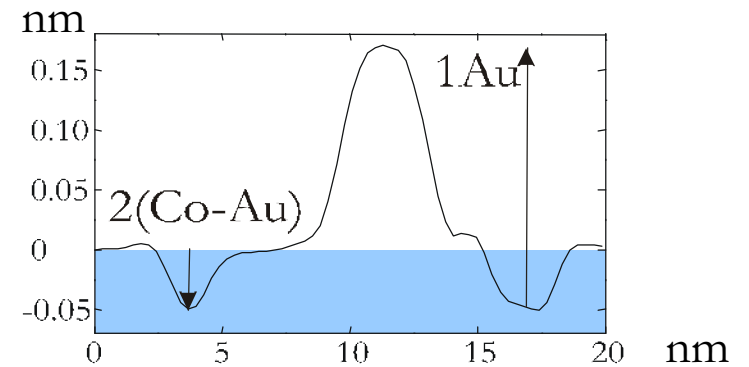
See also : Wollschläger *et al.*, *Surf.Sci.***277**, 1 (1992)

1ML Co hcp \approx 0.205nm

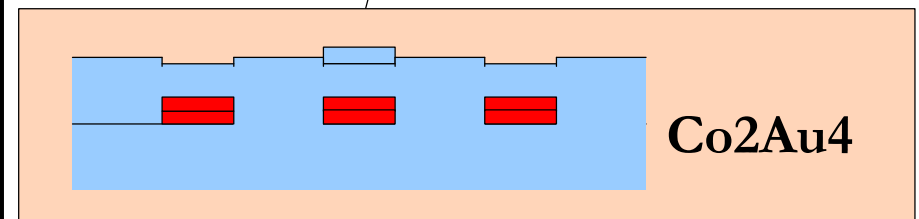
1ML Au fcc \approx 0.235nm

} Array of hollows

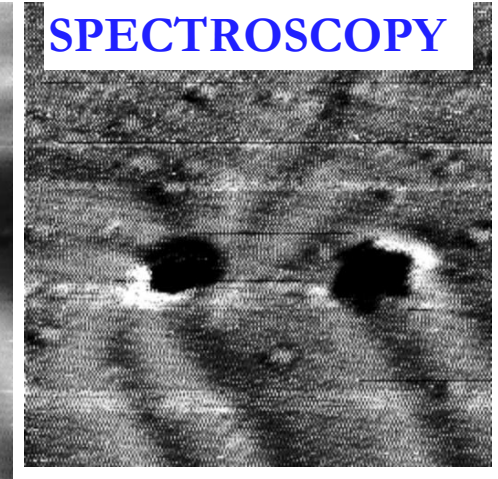
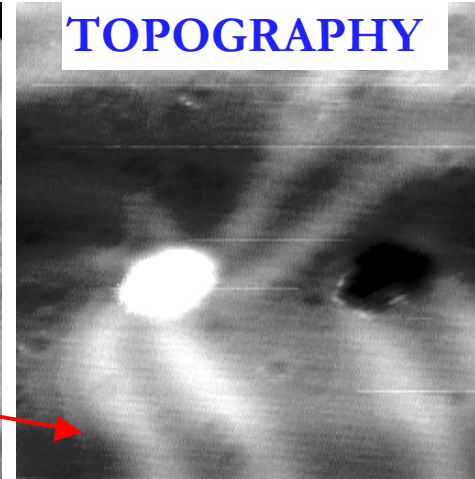
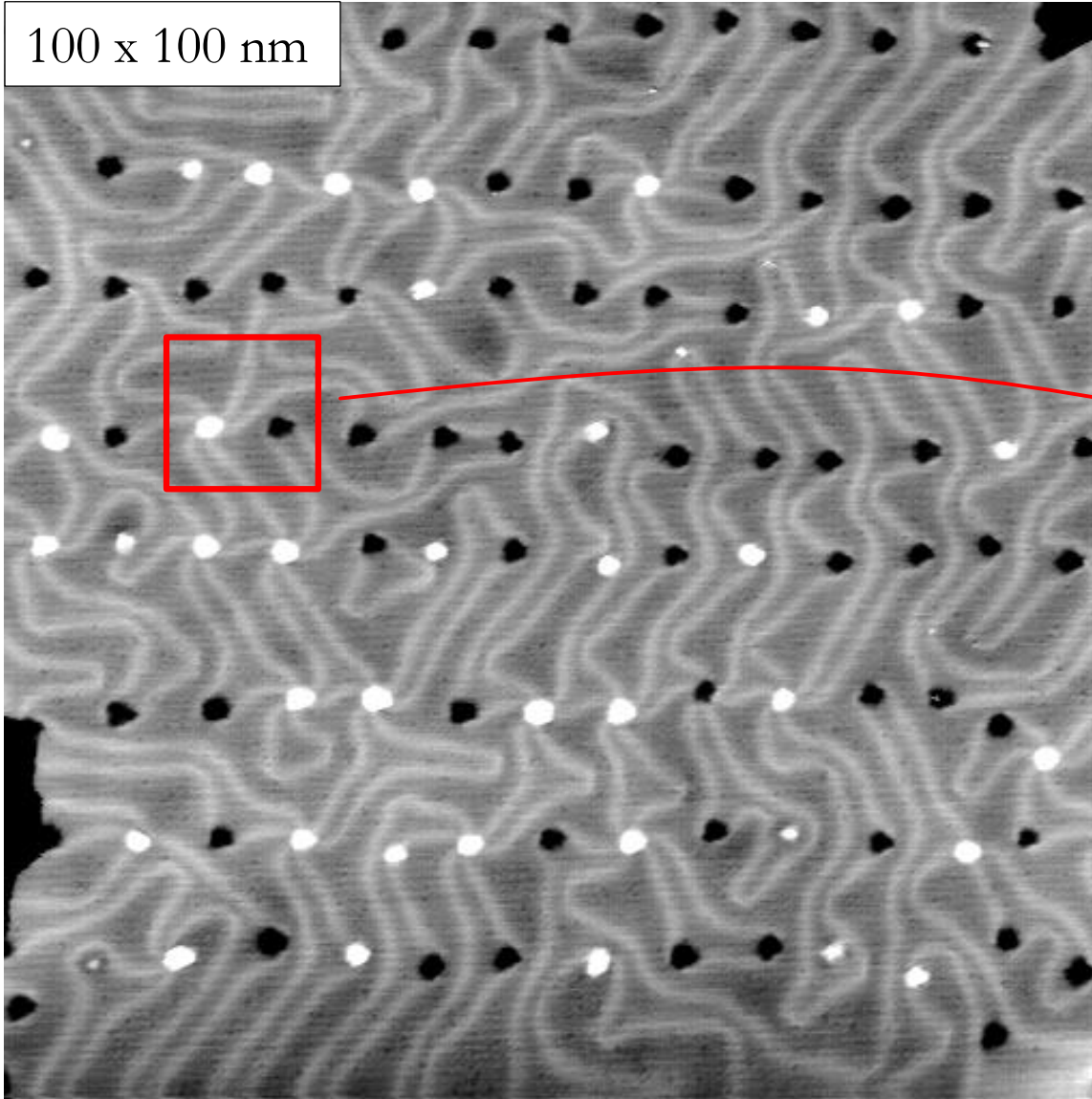
Typical cross-section :



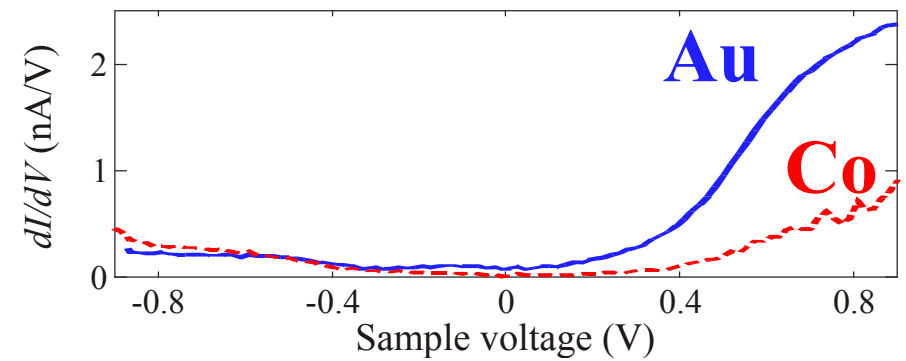
1ML Au decoration



- Surface smoothing
- Unaffected Co dots



SAME AREA

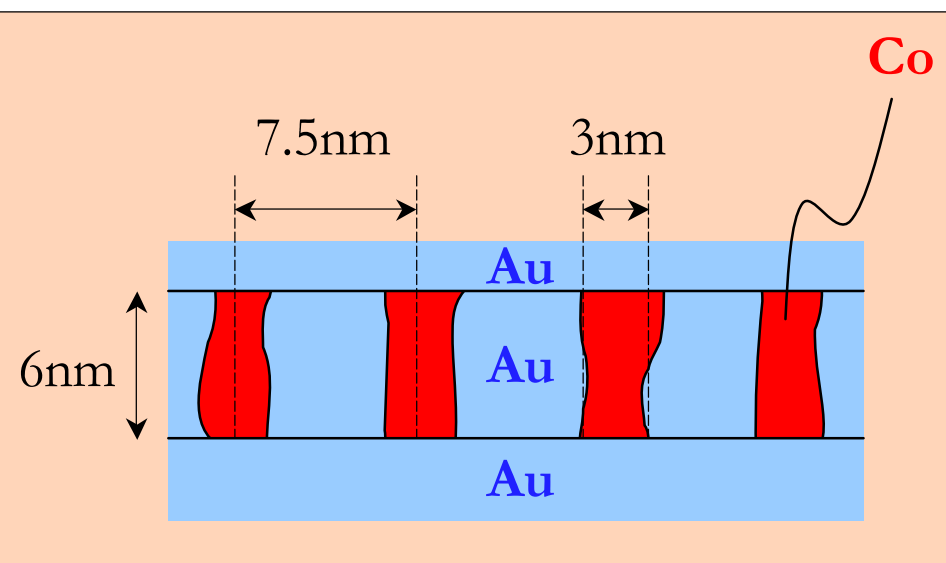
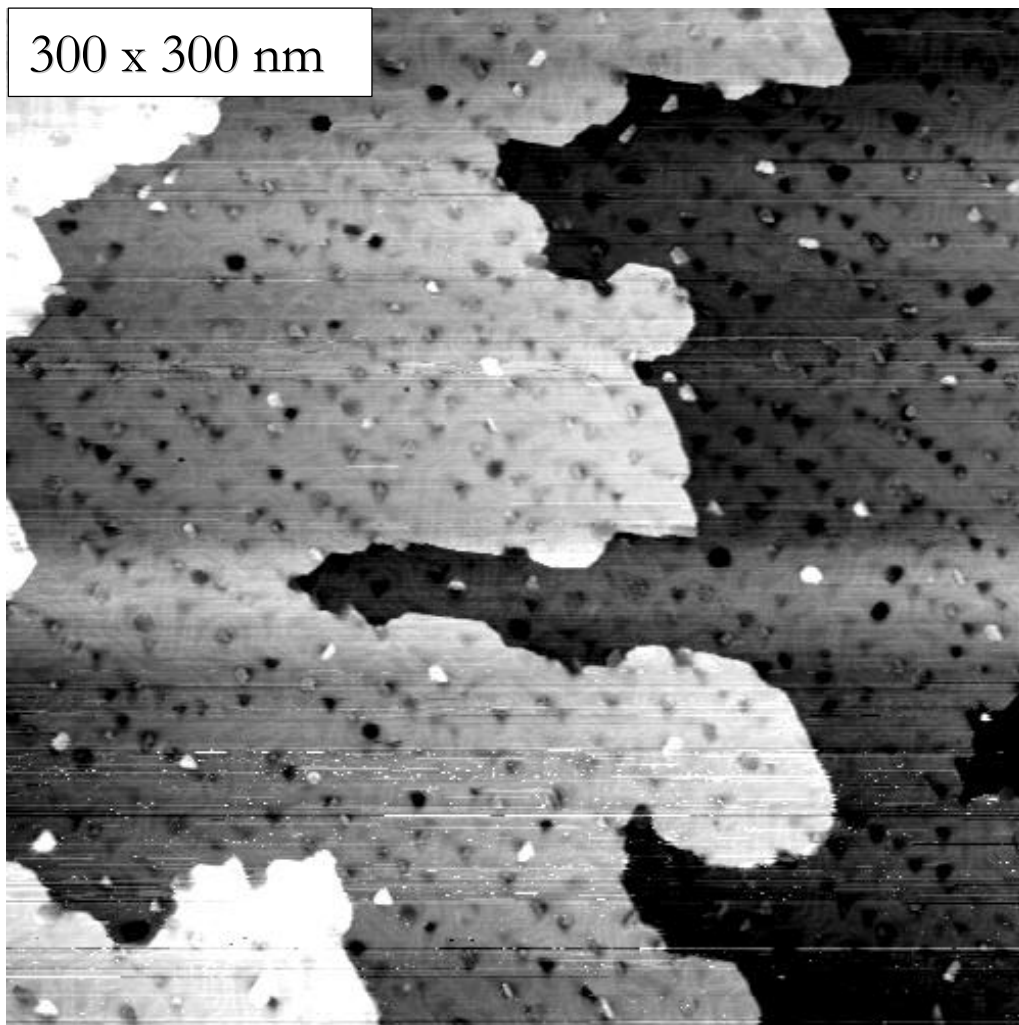


Co atoms grow only on existing dots

 VERTICAL SELF-ORGANIZATION



300 x 300 nm

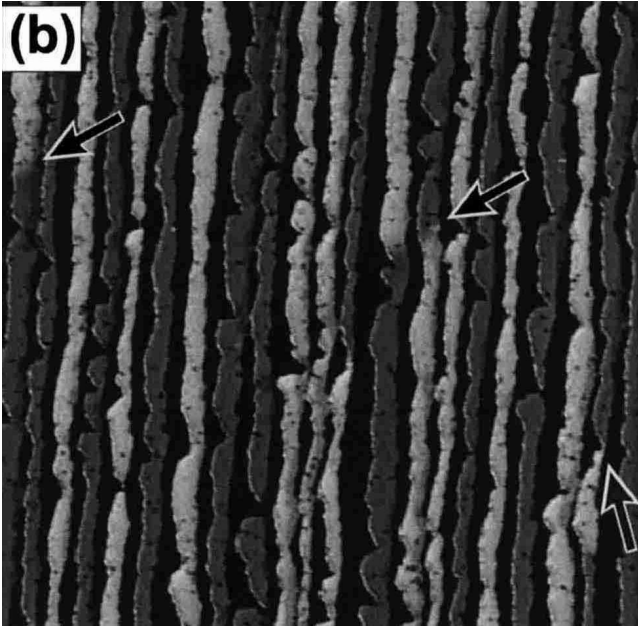


- Self-organization nearly undisturbed
- Pillars with 2:1 vertical aspect ratio
- Unclear to this point :
 - Exchange mechanism
 - Limiting factors ?
 - Composition, microstructure ?



ATOMIC LAYER RANGE : WETTING

↳ nanometer-world / surface physics



1.5AL on vicinal Fe/W(110)

M. Bode et al, J. Electr. Spectr. Rel. Phenom. 114- 116, 1055 (2001)

THICK DEPOSITS : NO WETTING

↳ micrometer-world / materials physics

Fe/Mo(110) (Pulsed Laser Deposition)

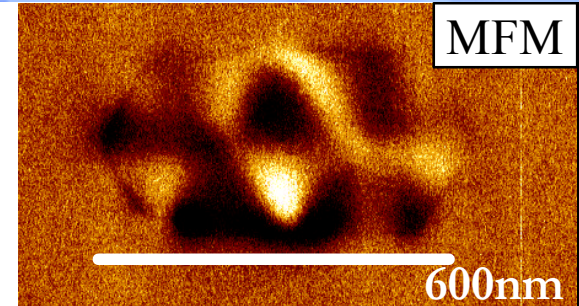


AFM, ~1 μm

MFM:

Y. Samson

(CEA/France)



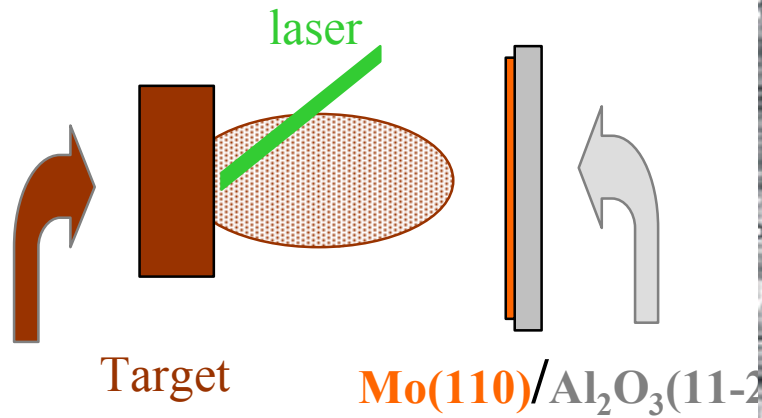
P.-O.Jubert et al., JMMM 226, 1842 (2002)

P.-O.Jubert et al., PRB64, 115419 (2002)

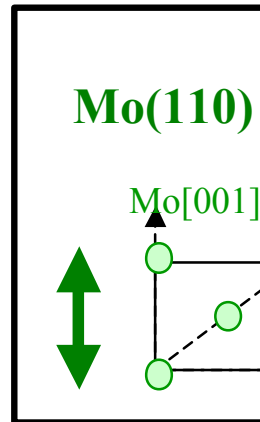
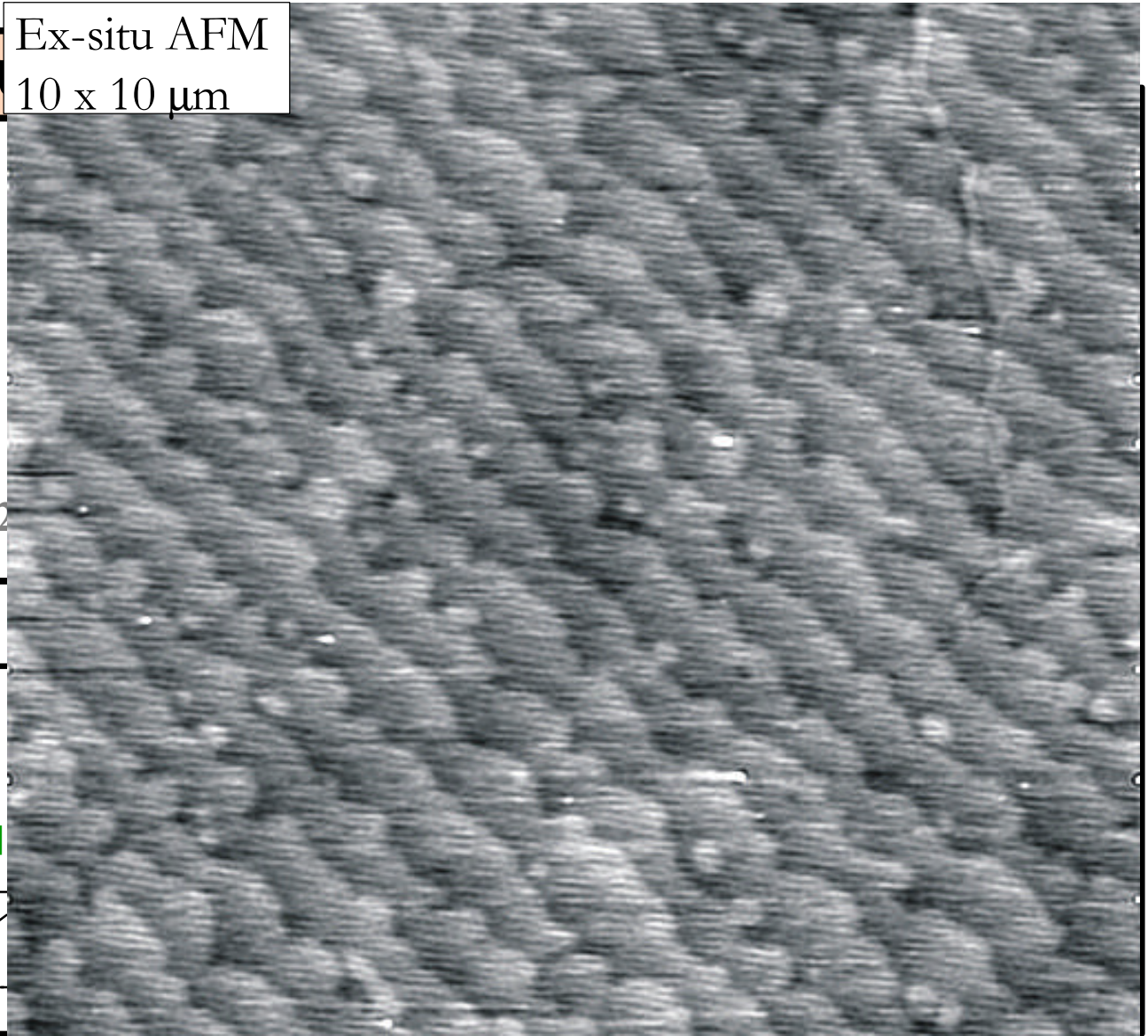
↳ Is there an intermediate world ?



PULSED LASER DEPOSITION,



Ex-situ AFM
10 x 10 μm

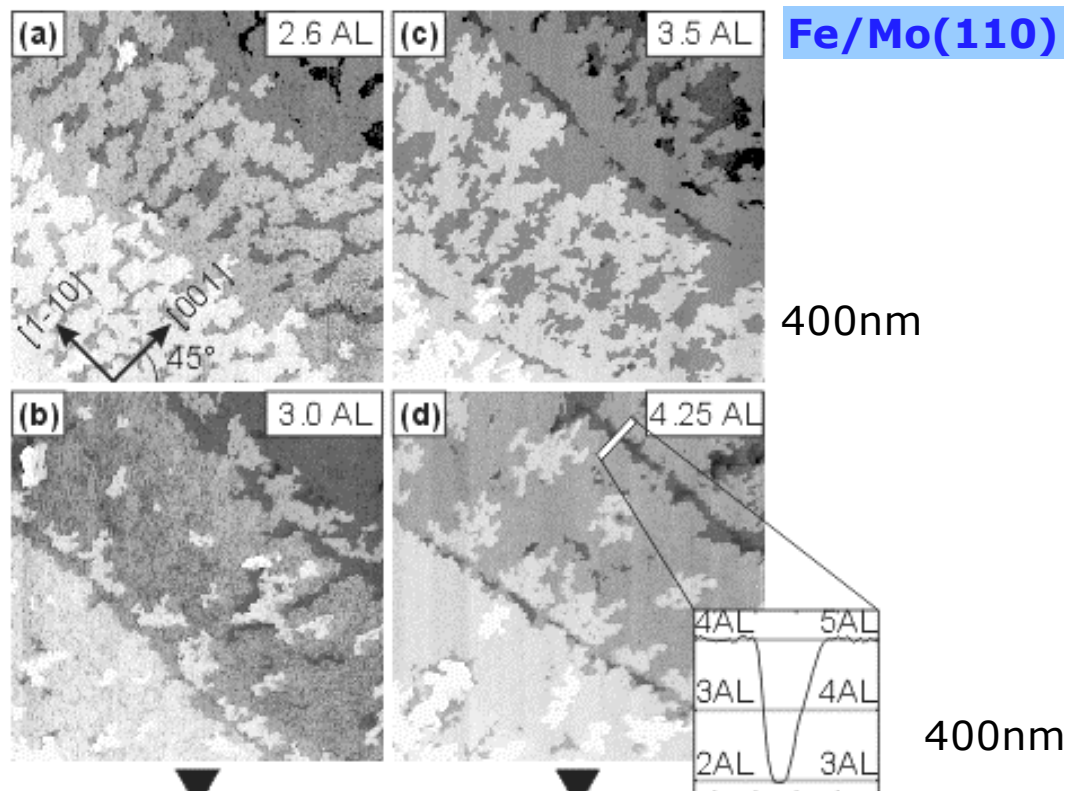


Buffer layer growth : **O. Fruchart, S. Jaren, J. Rothman, Appl. Surf. Sci. 135, 218 (1998)**

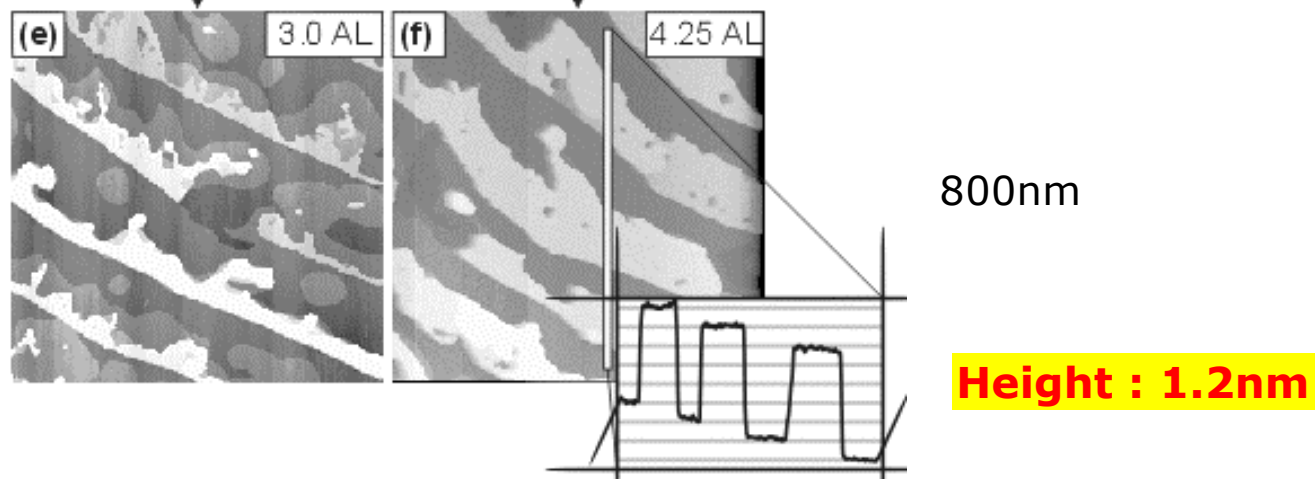




150°C deposition



450°C annealing





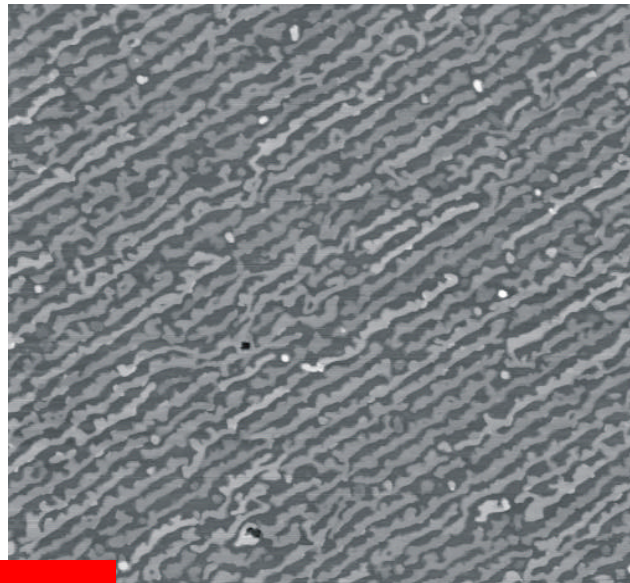
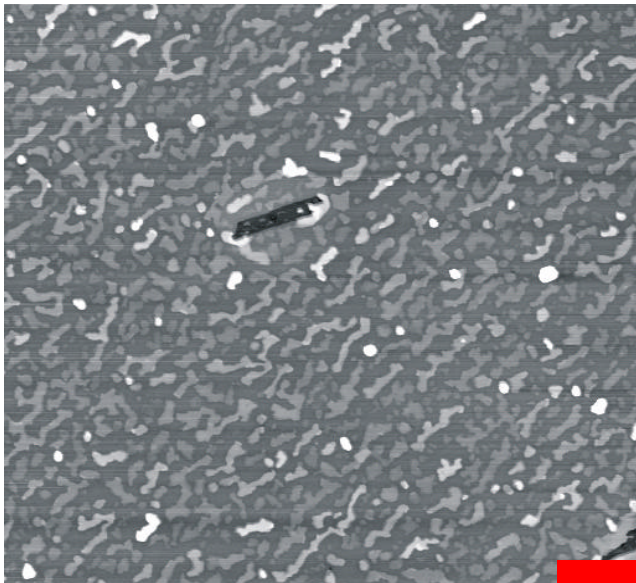
Sapphire\Mo(8nm)\interface\Fe(150°C, 450°C annealing)

1nm

2.5nm

Average thickness

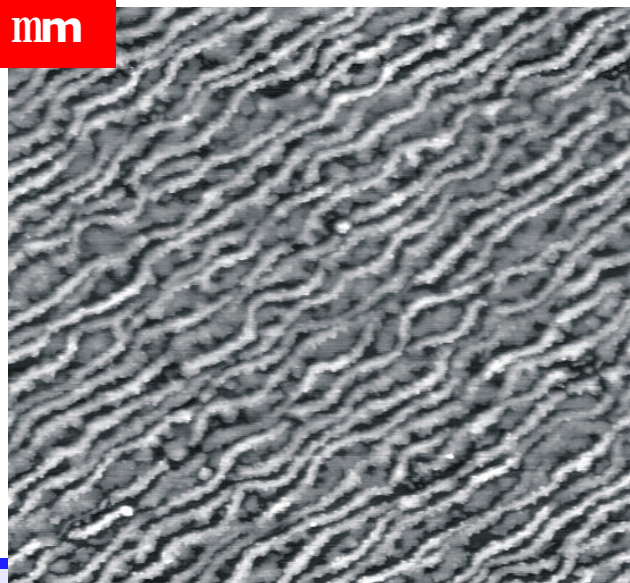
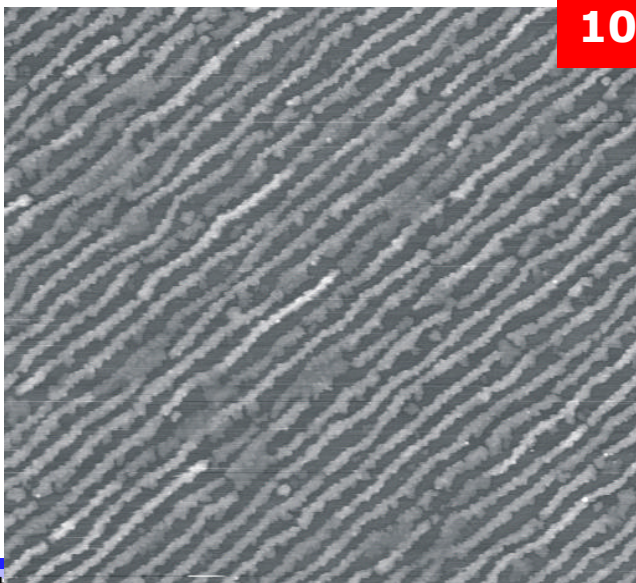
W(<1nm)



Height : 5nm

10 mm

Mo(raw)



Height : bimodal
1.5/4nm

Chemical
interface





(1. Introduction)

2. Self-assembled epitaxial growth

3. Self-organized epitaxial growth

4. 3D self-organization via multilayer stacking

 **5. Perspectives of self-organization**

6. X-ray investigation of SO systems

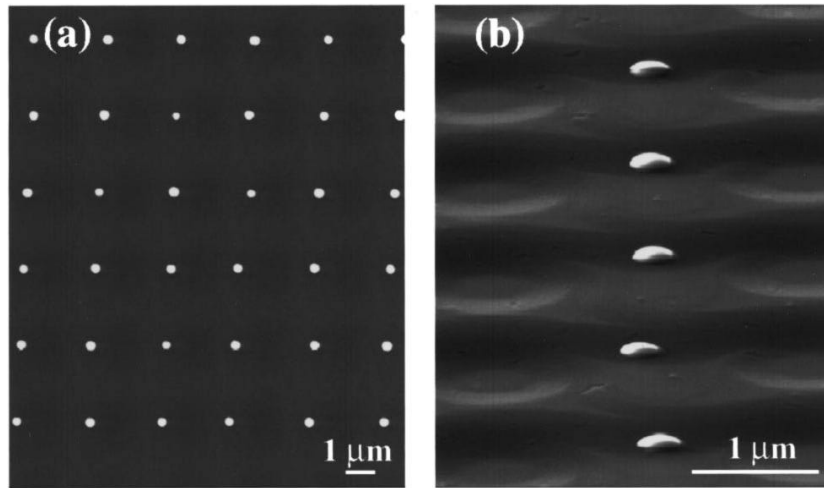
References





➤ Lithography + Etching + Annealing → holes

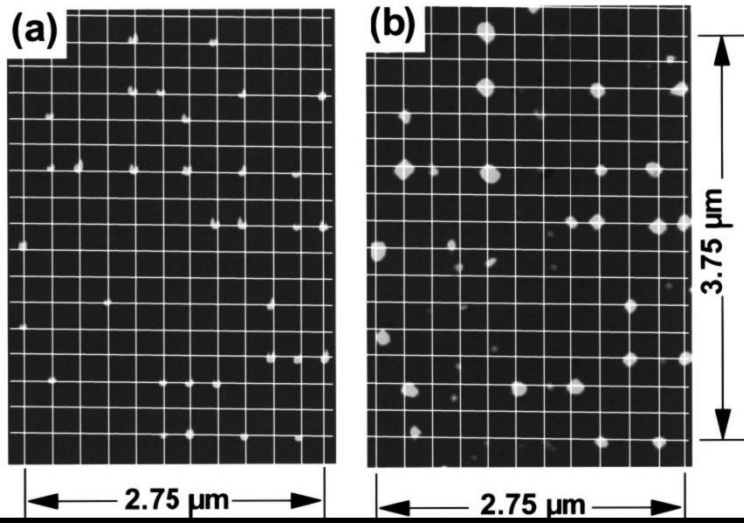
Au/Si



Y.Homma, Appl.Phys.Lett. **74**(6), 815 (1999)

T.Ogino, Surf.Sci.386, 137 (1997)

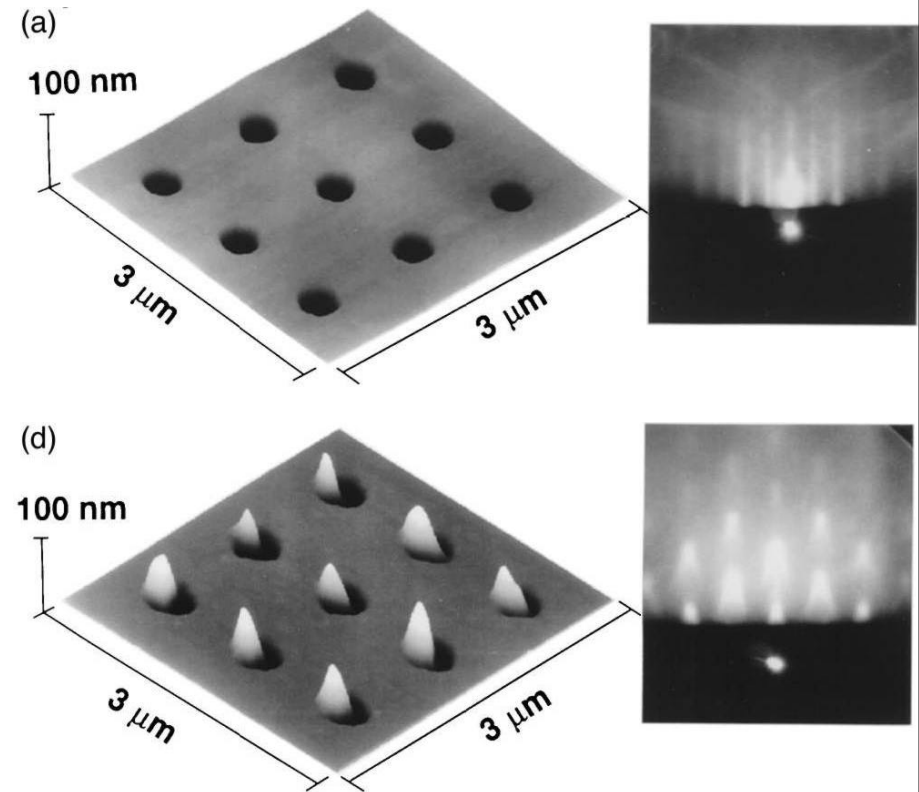
➤ Nanoimprint → Si mesas → Ge / Si



T.I.Kamins, Appl.Phys.Lett. **74**(12), 1773 (1999)

➤ In-situ lithography on oxide layer

InAs / GaAs



T.Ishikawa, Appl.Phys.Lett. **73**(12), 1712 (1998)



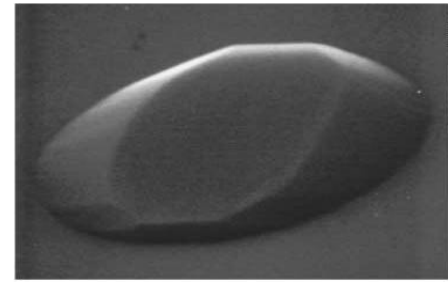


GaAs / GaAs

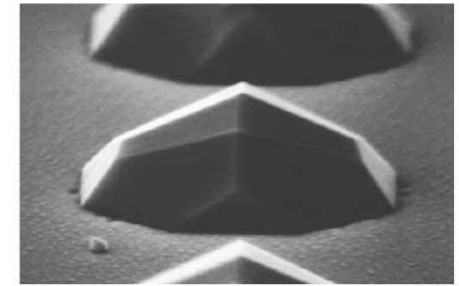
- **Step 1:** Deposition of SiO₂ layer
- **Step 2:** Ex-situ lithography on oxide layer, plus wet chemical etching
- **Step 3:** Growth of GaAs through windows, either in dot or antidot array.



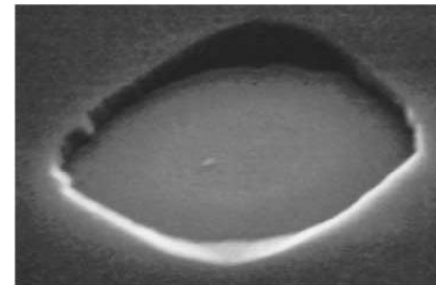
H. Hasegawa, *J. Cryst. Growth* 227-228, 1078 (2001)



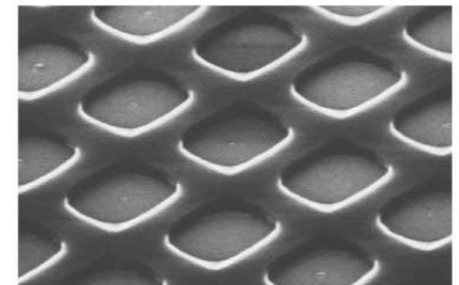
(a) 2μm



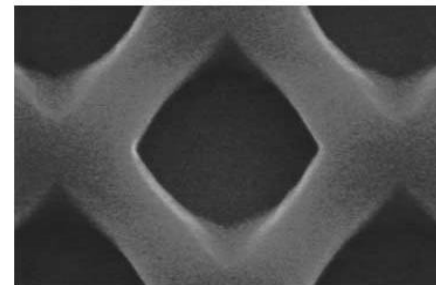
(b) 500nm



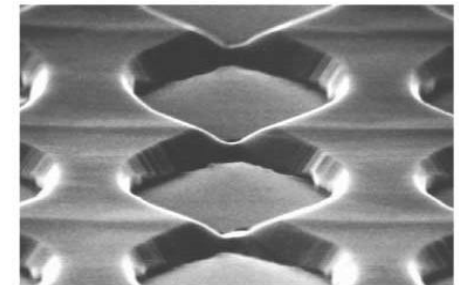
(c) 2μm



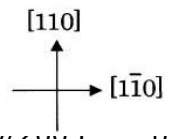
(d) 2μm

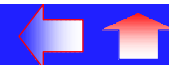


(e) 1μm

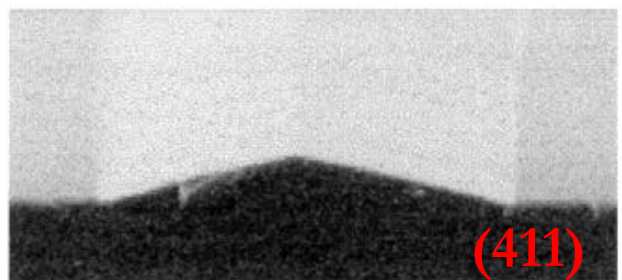
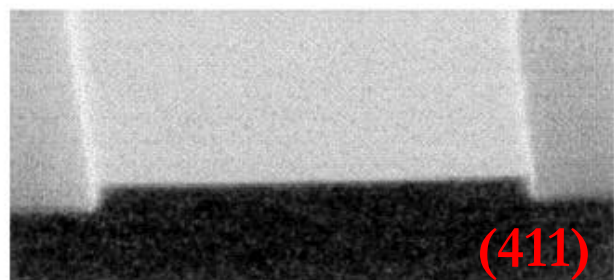
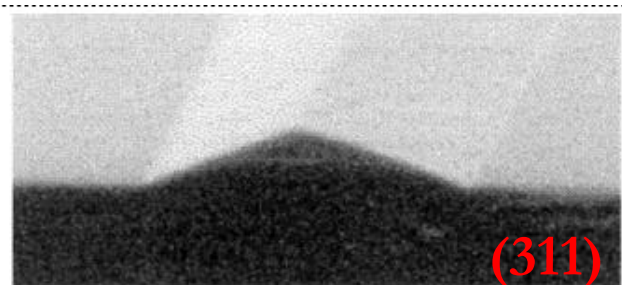
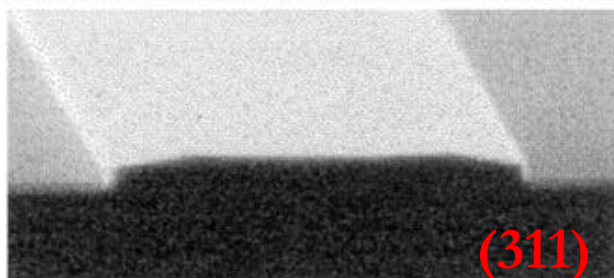
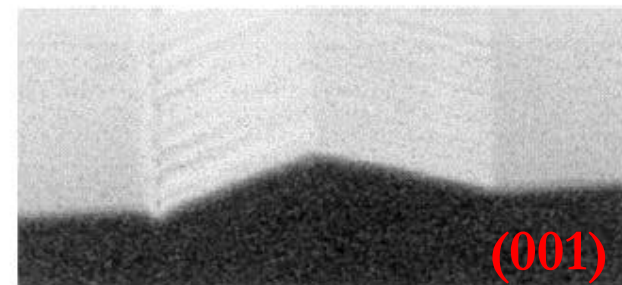
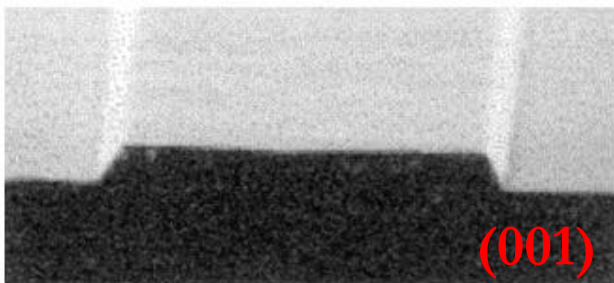


(f) 500nm





GaAs / GaAs



(e)



(f)

3mm wide stripes



H. Hasegawa, *J. Cryst. Growth* 227-228, 1078 (2001)





Surface Science 432 (1999) 37–53



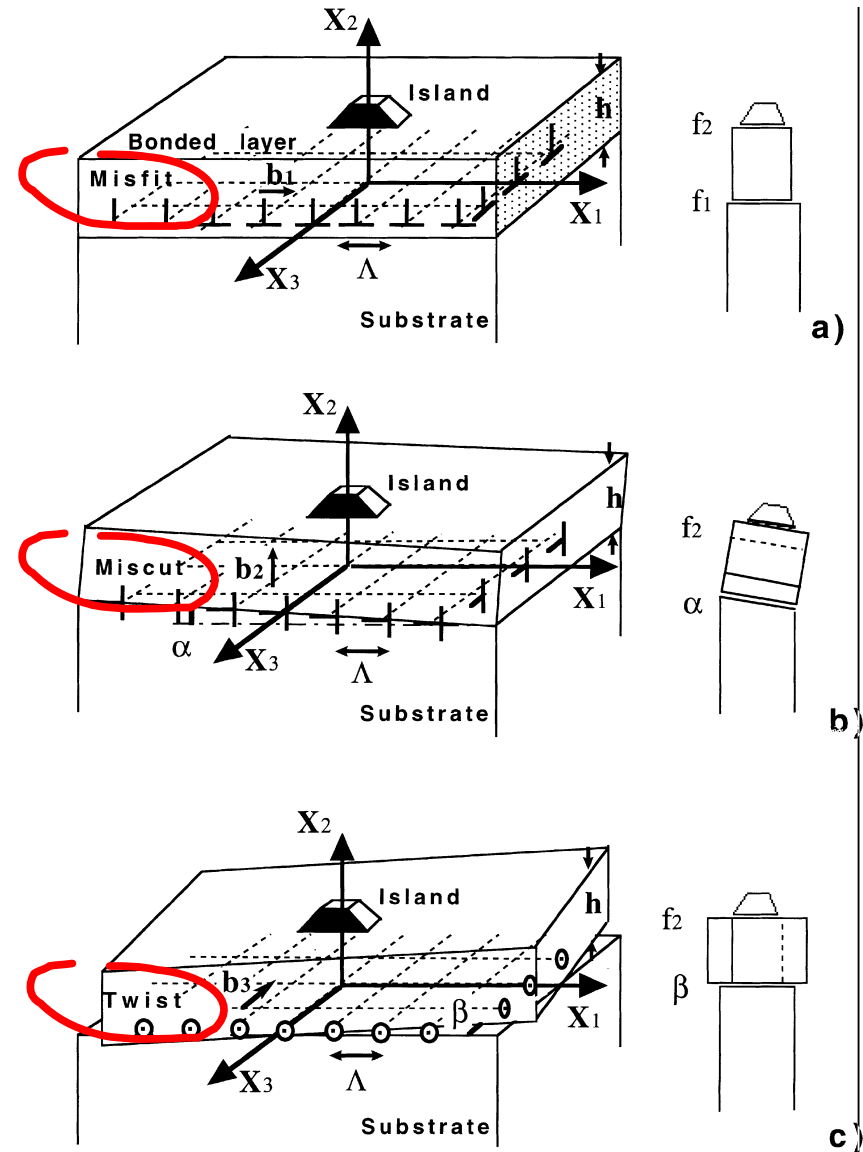
How to control the self-organization of nanoparticles by bonded thin layers

A. Bourret *

Département de Recherche Fondamentale sur la Matière Condensée, SP2M¹, CEA Grenoble, 17 rue des Martyrs 38054, Grenoble Cedex 9, France

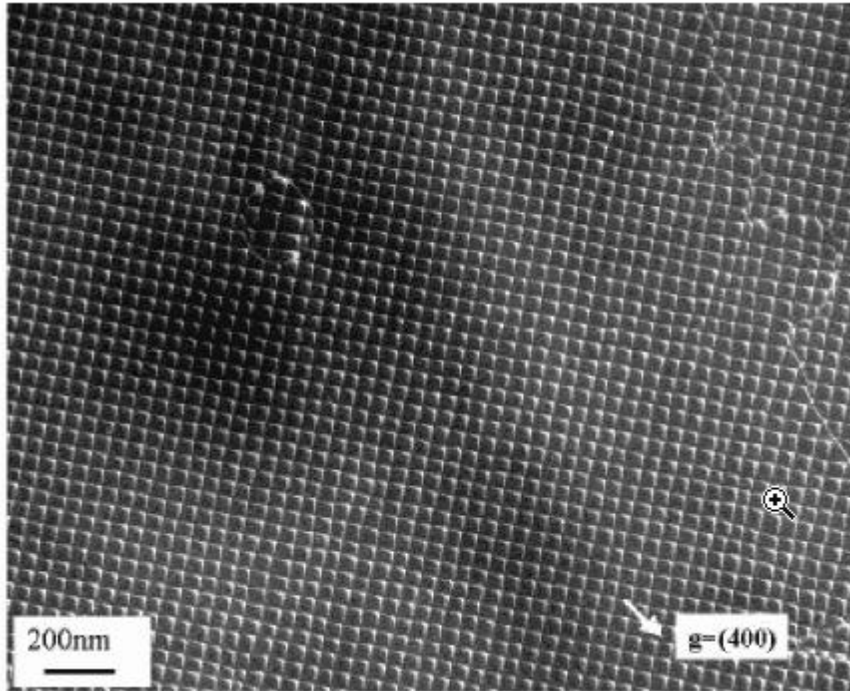
Received 21 December 1998; accepted for publication 6 April 1999

- Substrate bonding and smart cut process.
- ↳ array of dislocations arise from either:
- Misfit
 - Miscut
 - Twist



Step 1: wafer bonding

Screw dislocations

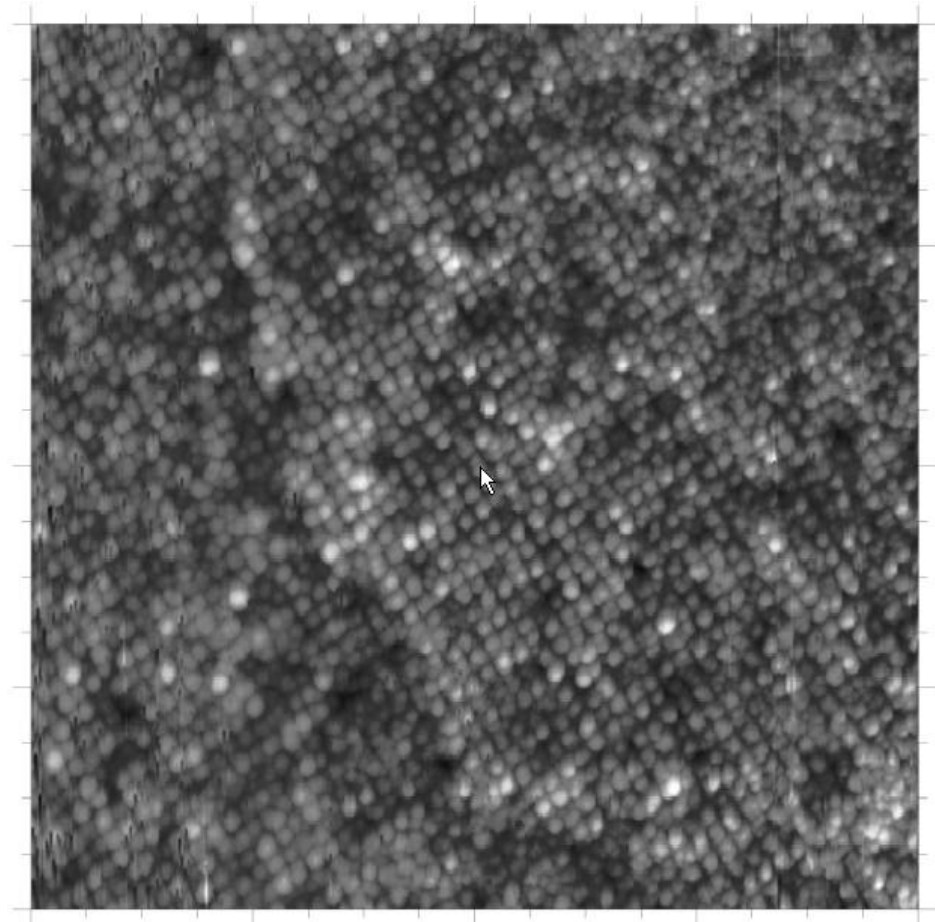


J. L. Rousseau *et al.*, APL80, 4121 (2002)

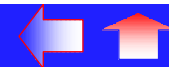
CEA-Grenoble

Step 2: template for growth

1. Chemical etching > corrugation enhanced
2. Growth (here: Si)

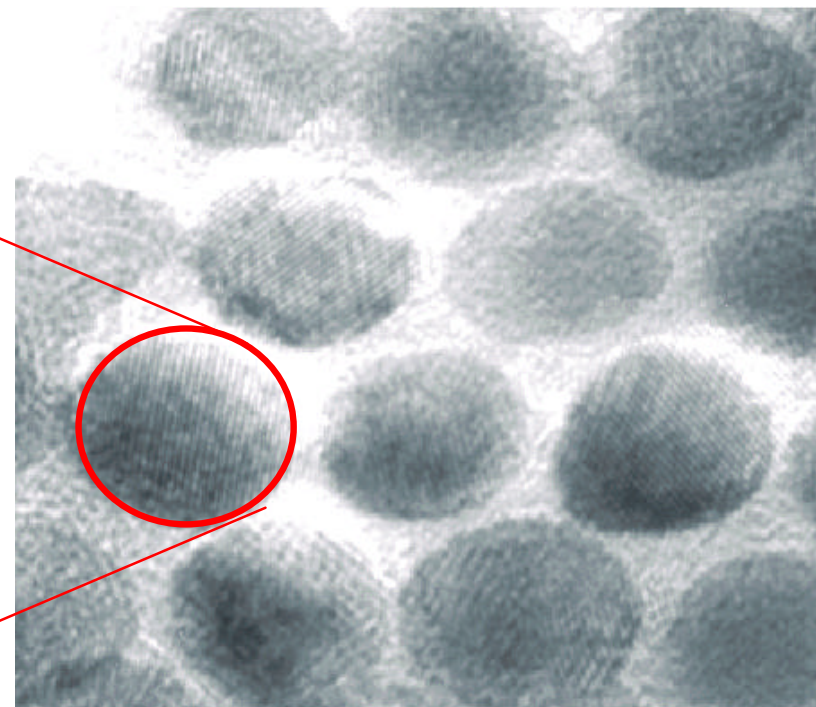
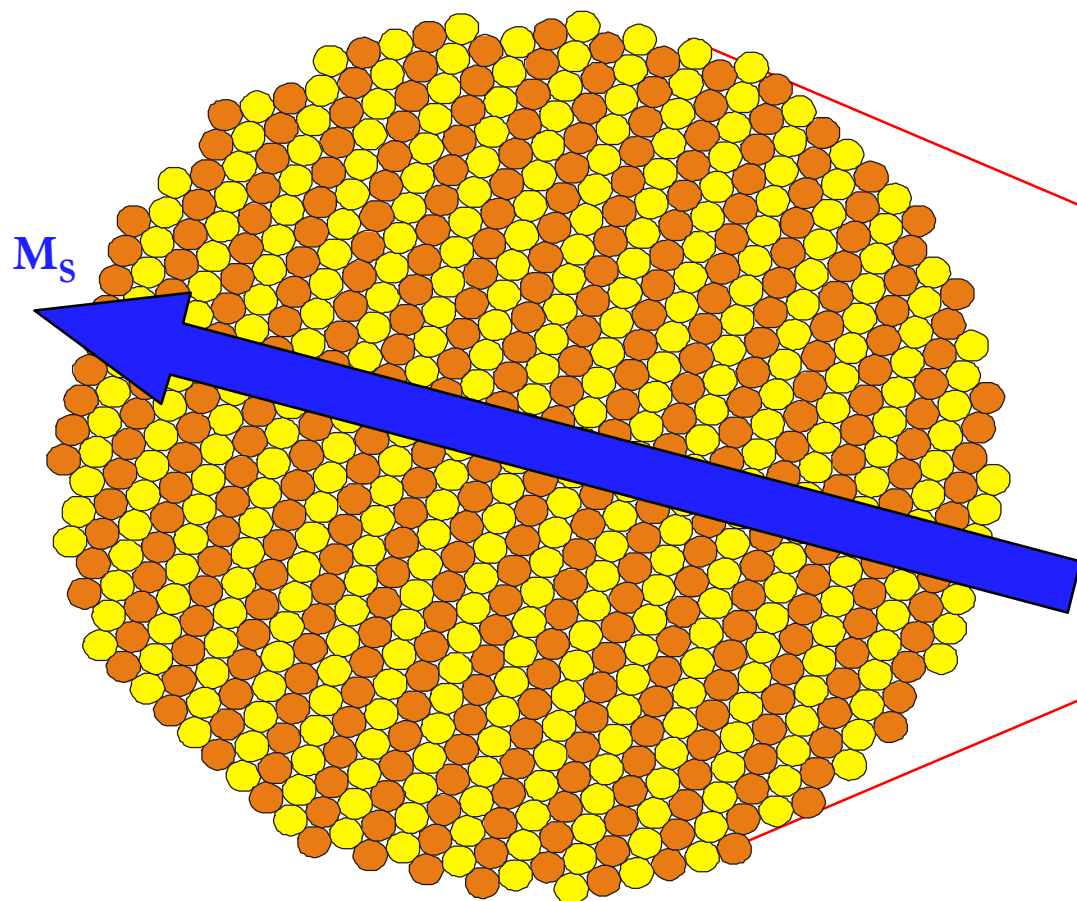


J. Eymery, Habilitation (2003)



$L1_0$ phase : alternation of Fe and Pt monoatomic planes

→ extremely high magnetocrystalline anisotropy K



Random orientation of anisotropy axes



S. Sun, *Science* 287, 1989 (2000)

(Image: courtesy of D. Weller - Seagate
via N. Dempsey - LLN/CNRS)



(1. Introduction)

2. Self-assembled epitaxial growth

3. Self-organized epitaxial growth

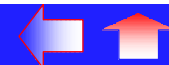
4. 3D self-organization via multilayer stacking

5. Perspectives of self-organization

 **6. X-ray investigation of SO systems**

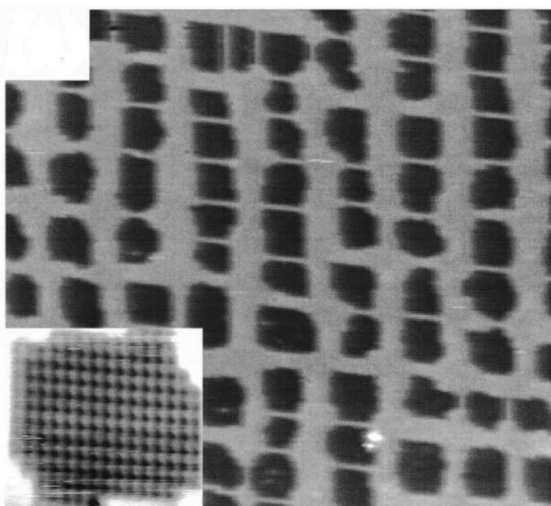
References





SXRD: self-organized N/Cu(001)

0.2AL N/Cu(001)



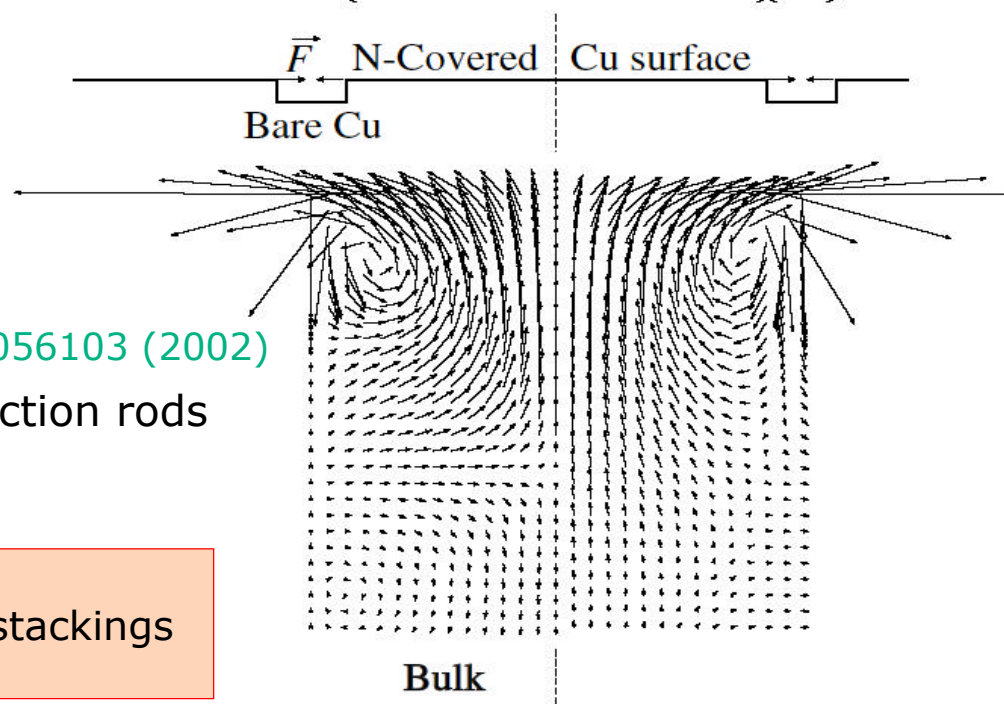
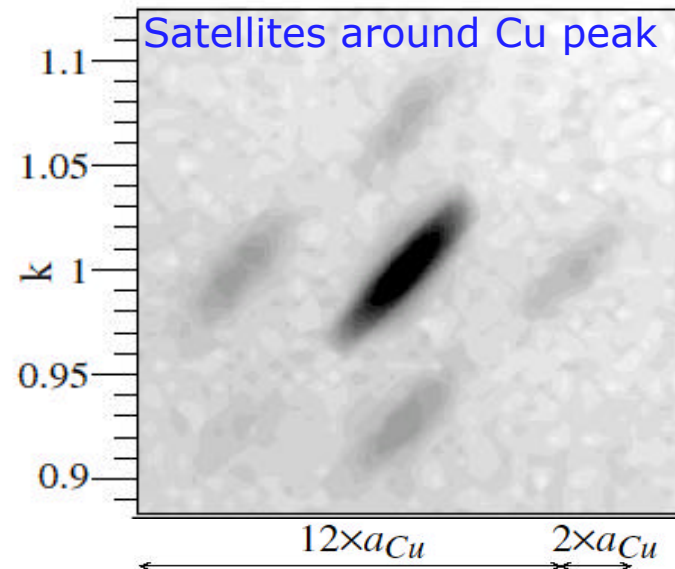
S.L. Silva, APL76, 1128 (2000)
F.M. Leibsle, SS317, 309 (1994)

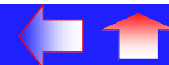
B. Croset, PRL88, 056103 (2002)

↪ Periodic surface strain give rise to satellite diffraction rods

Other groups:

T. Metzger (ESRF, Grenoble): Quantum dots stackings
J. Eymery (CEA Grenoble): wafer bonding





Collaborators



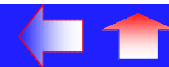
G. Renaud, M. Noblet, O. Ulrich
DRFMC/SP2M/IRS (CEA), Grenoble



J.-P. Deville, A. Barbier, F. Scheurer, J. Mané-Mané
IPCMS (CNRS/ULP/ECPM), Strasbourg



V. Repain, G. Baudot, S. Rousset
GPS-Jussieu, Paris

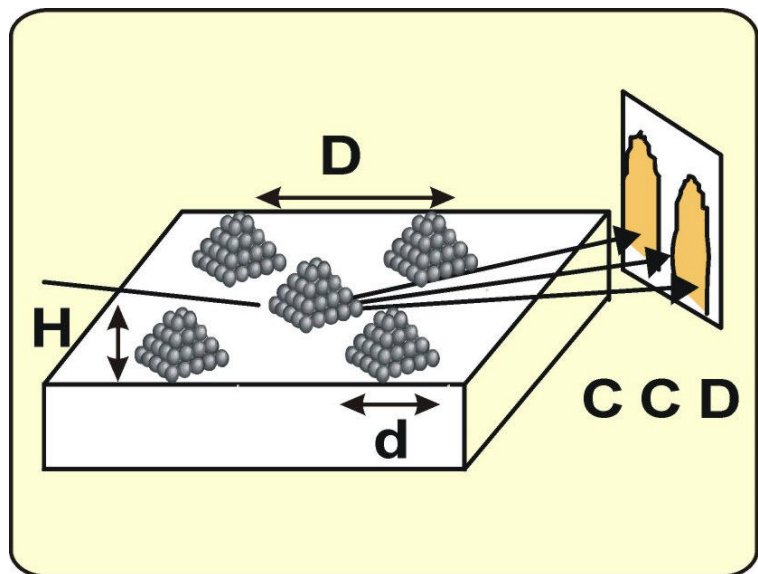


GISAXS: Grazing Incidence Small Ange X-ray Scattering

Objects \gg atoms

Surface sensitive

PRINCIPLE



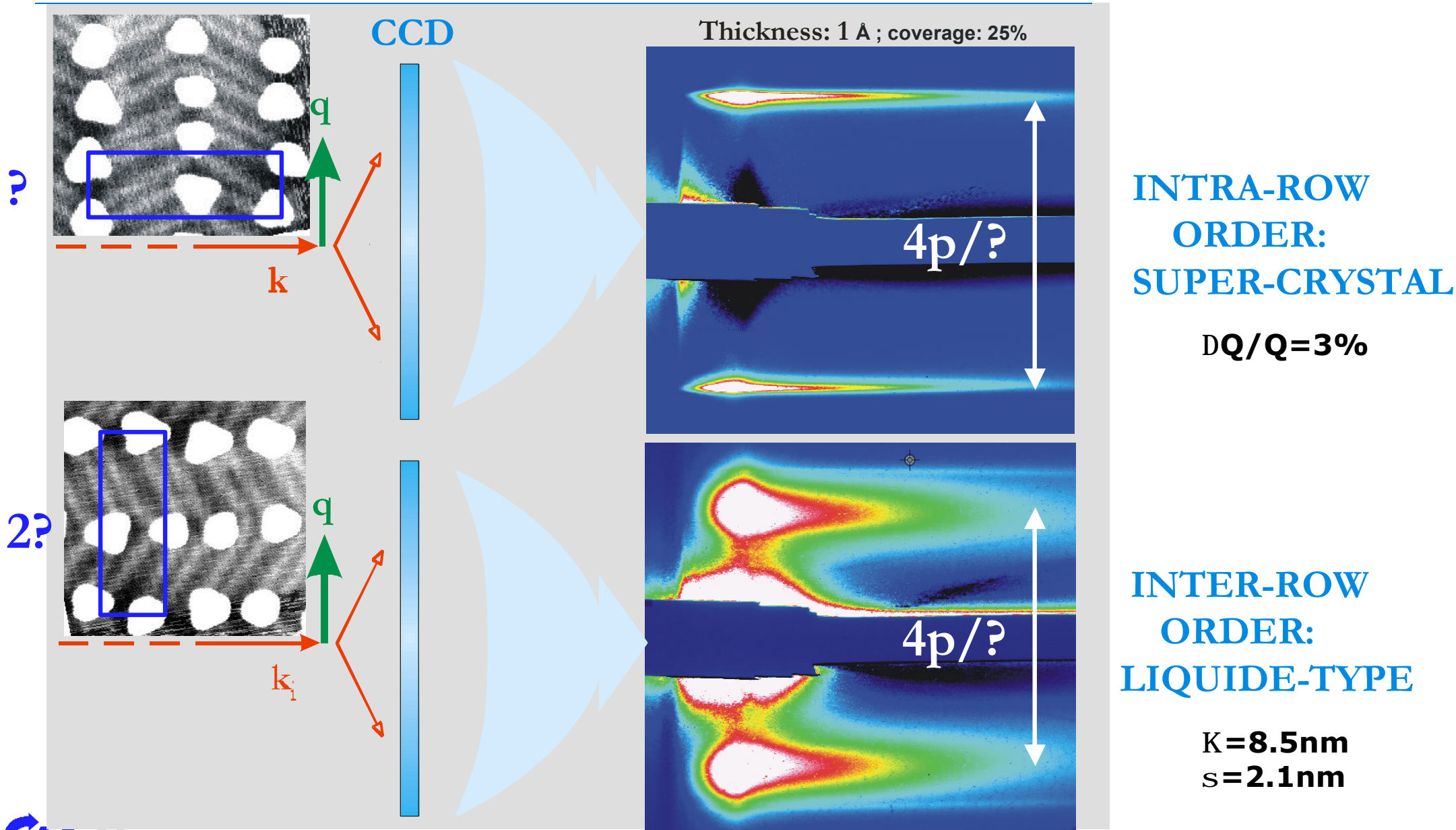
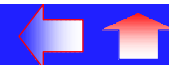
- In-plane / out-of-plane diffusion
- Probes size (H,d), shape, correlations

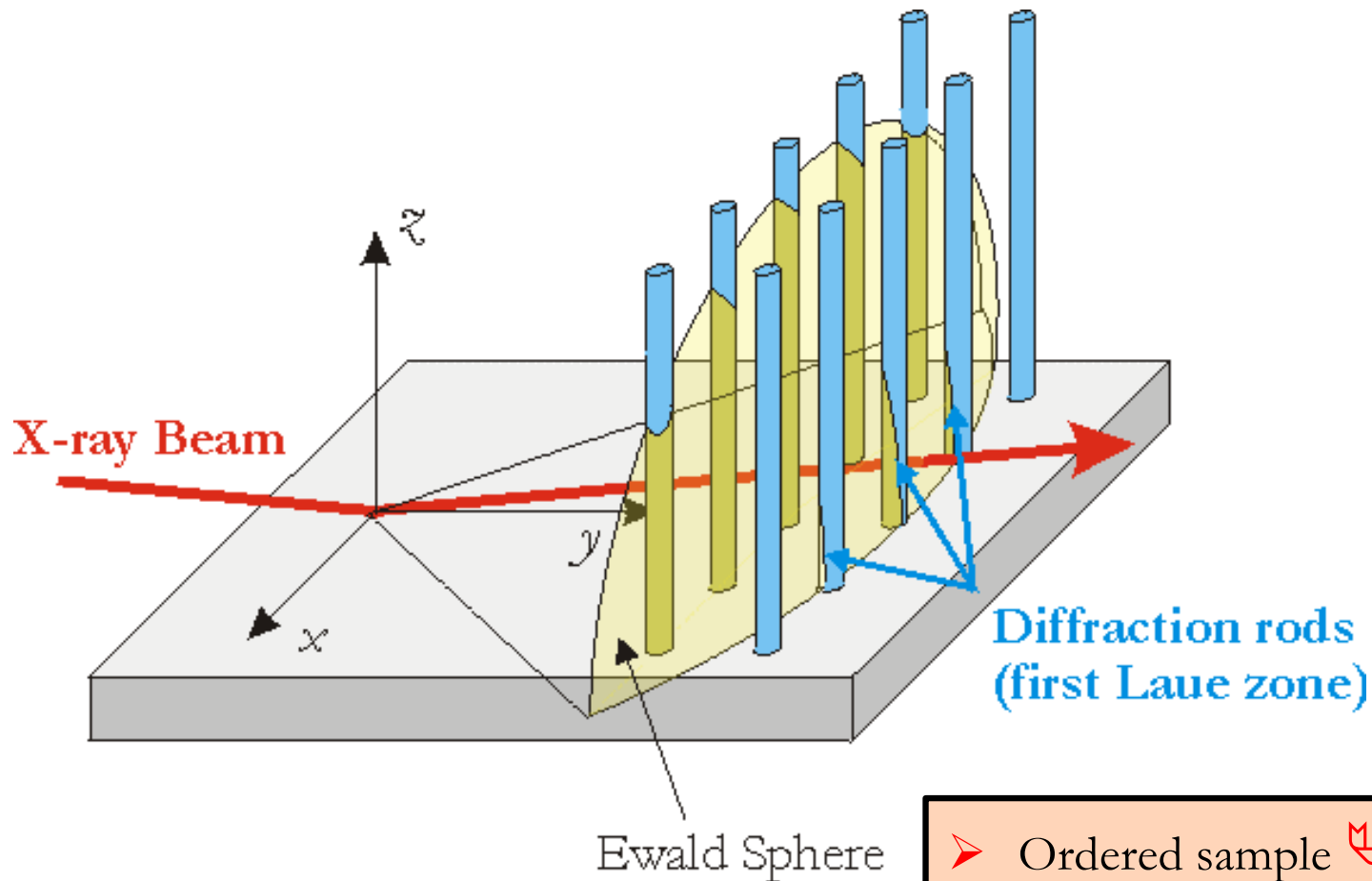
TECHNICAL ASPECTS

- ID32 beamline at ESRF
- In-situ under UHV:
 - real time
 - background subtraction
- No window before sample : low background

G. Renaud et al., Science 300, 1416 (2003)

O. Fruchart et al., Europhys. Lett. 63, 275 (2003)





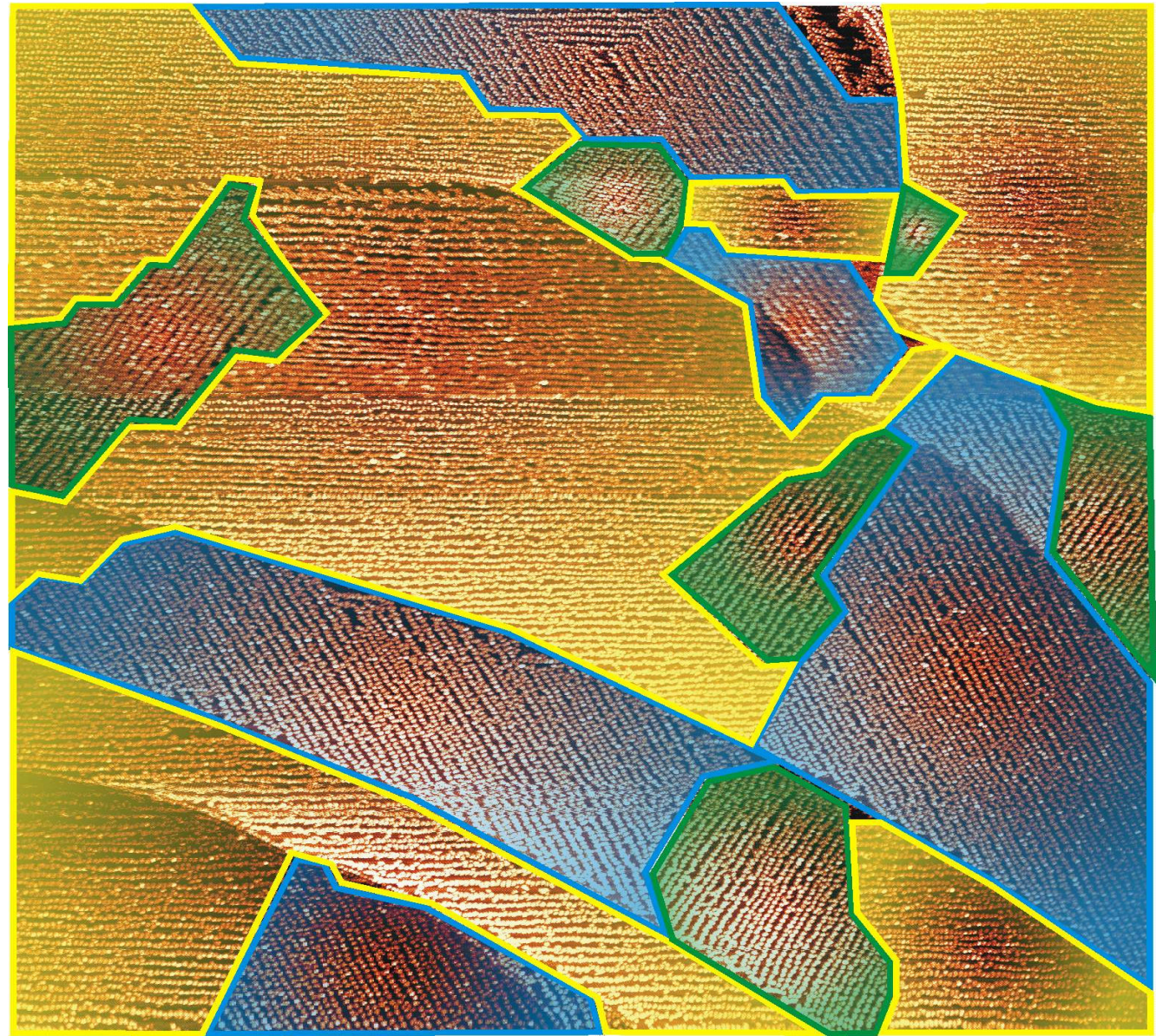
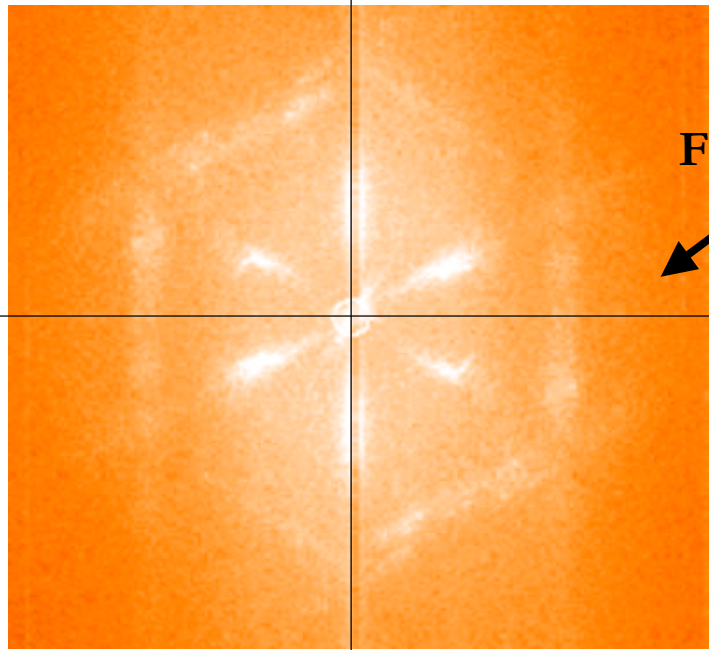
- Ordered sample ↪ 'super' reciprocal space ?
- Grazing incidence and 2D detector
 ↪ similarity with RHEED



1.5mm x 1.5mm STM image

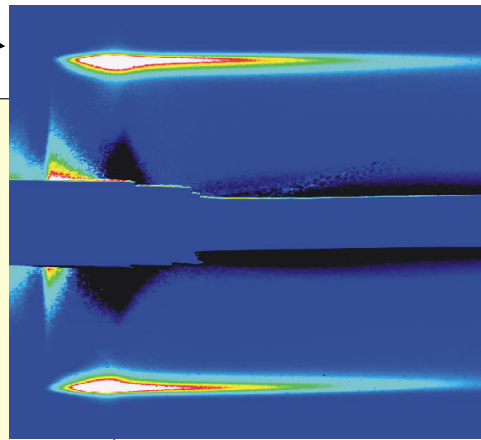
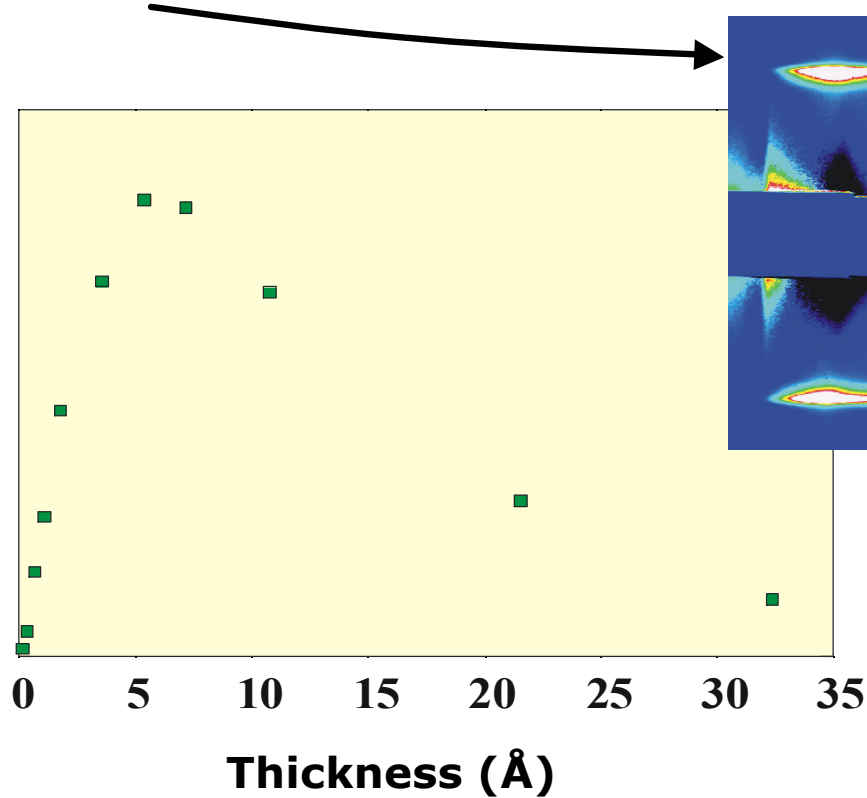


3-fold symmetry of Au(111) crystal
➤ 3 'equivalent domains'

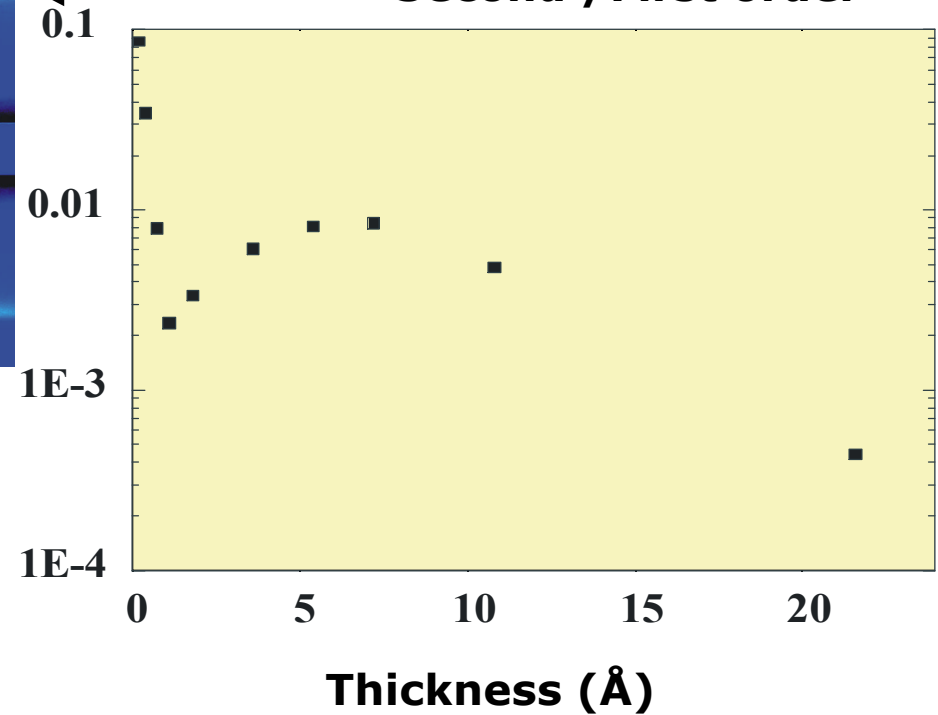




First order peak intensity



Second / First order



Features to explain

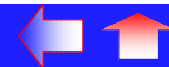
↪ Maximum at 6Å = 3 atomic layers ?

↪ Significant intensity for continuous film ?

↪ Weak intensity ?

↪ Intermediate minimum ?





RATIO: Second / First order peak intensity

➤ Deposition rate calibration

Simple model of 1D coalescence

